

SYSTEMS AND METHODS FOR MODULATED IMAGE CAPTURE

TECHNICAL FIELD

The present disclosure relates generally to pixel elements and image sensors; and more specifically, to systems for capturing images.

- 5 Moreover, the present disclosure also relates to methods for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element.

BACKGROUND

- An ability to quickly steer charge generated in an image sensor to multiple collection nodes is a key operation in, for example, Time-of-Flight (ToF) imaging. The switching between collection nodes can be done with conventional CMOS transistors, or by steering the charge within the sensor itself. For example, it is possible to use a pinned photodiode, and use CMOS switch transistors to select the capacitor where charge at a given time is stored. In a bridge circuit, the current from the photodiode is sampled to a capacitor so that the polarity of the capacitor alternates between each cycle. In modulated ToF circuits, charge is aggregated to the capacitor via multiple measurement cycles, where the duration of each cycle is very short. In a bridge circuit, the parasitic capacitances limit the accumulated voltage as well as modulation speed due to the short cycle time.
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- In order to avoid limitations caused by parasitic capacitance, there are approaches that avoid CMOS switches, and the charge is steered to different collection nodes within the sensor itself. An example of such a sensor is described in a published paper, titled *A Range Image Sensor Based on 10um Lock-In Pixels in 0.18um CMOS Imaging Technology*, by David Stoppa et al., IEEE JSSC, 2011. The sensor is a pinned photodiode with two floating diffusions. The charge is steered to either of the floating
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diffusions with gates G1 and G2. The structure is called a pinned demodulator. In order to make the sensor react faster, the gates G1 and G2 extend further above the pinned photodiode. This helps in rapidly transferring the photogenerated charge from the pinned photodiode to the floating diffusion. Such buried channel demodulator requires a transparent gate material.

It is also possible to steer the charges to different sensor nodes using a charge coupled device (CCD) as highlighted in a published paper, titled *Robust Optical Time-of-Flight Range Imaging Based on Smart Pixel Structures* , by Bernhard Buttgen et al., IEEE TCAS-I, 2008.

A photogate-based circuit described in a published paper, titled *Pulsed Time-of-Flight 3D-CMOS Imaging Using Photogate-Based Active Pixel Sensors* , by Andreas Spickermann et al., ESSCIRC 2009, uses a photogate sensor. The charge from the photogate can be transferred to four floating diffusions using four transfer gates. A pulse emitted by a laser is reflected back to the sensor, and the reflected pulse is measured with four measurements, each steered to a different floating diffusion.

A granted US patent US6580496 B2, titled *Systems for CMOS-Compatible Three-Dimensional Image Sensing Using Quantum Efficiency Modulation* , 2003, describes a quantum efficiency modulation principle in a photodetector. The quantum efficiency modulation works so that the cathodes of two photodiodes adjacent to each other are pulsed high and low alternately using voltage sources. Between the voltage sources and the cathodes, there is a capacitor so that the collected charge remains in the cathode. When charge is collected to the right-side cathode, the left-side cathode (n+) voltage is set lower, and the right-side cathode voltage is set higher. Thus, the right-side depletion region has a larger volume, and, consequently, higher quantum efficiency. There is also a gate between the two cathodes that can be used to reduce leakage between the cathodes. The approach of US6580496 B2 has some disadvantages.

First, since the pulsed voltage sources connect to the cathodes via a capacitor, the capacitance of the capacitor needs to be large in comparison to the cathode capacitance. Also, because the cathode capacitance is relatively large, the modulation effect is not very strong since the change in the depletion region volume due to modulation is modest. The strength of the modulation effect can be defined by modulation contrast, which is the ratio between the maximum and minimum quantum efficiency resulting from the modulation.

Modulating the quantum efficiency by changing the depletion region volume via the capacitive connection to the collection node is not very efficient. In order to improve the modulation contrast, a published paper, titled *A 0.13 μm CMOS System-on-Chip for a 512×424 Time-of-Flight Image Sensor With Multi-Frequency Photo-Demodulation up to 130 MHz and 2 GS/s ADC*, by Cyrus S. Bamji et al., IEEE JSSC 2015, describes use of polysilicon gates (PG) above two n-diffusions that are separated by a p-type potential barrier. This way, either an n-doped region under PG A or an n-doped region under PG B attracts charges. This leads to a good modulation contrast. A p-doped barrier between the n-doped regions prevents charge from flowing between A and B diffusions.

Implementations described in Bamji can be used for modulated time-of-flight applications. The idea in Modulated Time-Of-Flight (MTOF) applications or Pulsed Time-Of-Flight (PTOF) applications is explained for example in a journal, *Sensors* 2015, Vol. 15, 4624-4642; doi:10.3390/s150304624. In both MTOF and PTOF, there is a need to collect photogenerated charge into different storage nodes depending on the time the charge was generated, and rapidly switch between storage nodes.

FIG. 0A represents prior art, and shows a side view of a semiconductor substrate **192** that is of a first conductivity-type semiconductor material. Also shown is a backside conductive layer **198** that is a second

conductivity-type semiconductor material. Note that first and second conductivity-type semiconductor materials can be either acceptor doped (p-type semiconductor) or donor doped (n-type semiconductor). For example, if the first conductivity-type semiconductor material is an n-type semiconductor, then the second conductivity-type semiconductor material is a p-type semiconductor. In FIG. 0A, a node **194** is a second conductivity-type semiconductor material, and a deep well **195** is made of a first conductivity-type semiconductor material. The voltage of the backside conductive layer **198** can be set by connecting, for example, a wire to it. However, there are other ways to set the voltage of the backside conductive layer **198** that may be more preferred. For example, there need not be a physical wire connecting a voltage source to the backside conductive layer **198**. Below, we describe such means to set the voltage of the backside conductive layer **198**.

Assume an example where the first conductivity-type semiconductor material is an n-type semiconductor material. Thus, in FIG. 0A, the node **194** is a p-type semiconductor material, the deep well **195** is an n-type semiconductor material, the backside conductive layer **198** is a p-type semiconductor material, and the substrate **192** is an n-type semiconductor material. Also, the substrate **192** is a high resistivity semiconductor material (for example, having resistivity in an order of kilo Ohm-cm for silicon at room temperature).

When the node **194** is set to a large negative voltage, for example, such as -30V, punch-through happens through the substrate **192**, so that a large negative voltage, for example, -15V (notably, the exact value depends on substrate doping level, geometries and dimensions) is conveyed to the backside conductive layer **198**. Such punch-through biasing is explained in a granted US patent US4837607, titled *Large-Area, Low Capacitance Semiconductor Arrangement*, by inventors J. Kemmer and G. Lutz, 1989, and a published paper, titled *A Radiation*

Detector Design Mitigating Problems Related to Sawed Edges , by A. Aurola et al., Int. C. Position Sensitive Detectors, 2014, which are hereby provided as references. Note that CMOS transistors can be built into the deep well **195**. Also, note that instead of using the deep well **195**, a
 5 simple n-well **196** (namely, of a first conductivity type) and a p-well **197** (namely, of a second conductivity type) could be used for building transistors into. Furthermore, in order for the punch-through biasing to work, there needs to be a large enough distance between the wells (**195** and **196**) and the node **194**. For example, a distance between the well
 10 **195** and the node **194**, as well the n-well **196** and the node **194** need be large enough. In the above example, the wells **195** and **196** could be biased to 5V and the well **197** to 0V.

Another variant of the backside biasing is a generally known method illustrated in FIG. 0B. The node **194** is a second conductivity-type
 15 semiconductor material, a substrate **193** is a high resistivity second conductivity-type semiconductor material, the backside conductive layer **198** is a second conductivity-type semiconductor material, the deep well **195** is of a first conductivity-type semiconductor material, the well **196** is of a first conductivity-type semiconductor material, and the well **197**
 20 is of a second conductivity-type semiconductor material. In this case, the node **194**, the substrate **193** and the backside conductive layer **198** are made of a second conductivity-type semiconductor material.

When, assuming in the example that the first conductivity-type semiconductor material is an n-type semiconductor material, the aim is
 25 to set the voltage of the backside conductive layer **198** to a large negative potential, for example, -15V. In this case, the node **194**, the substrate **193** and the backside conductive layer **198** are a p-type semiconductor material. If the backside conductive layer **198** does not need to drive large currents (which is the case in the context of the
 30 present disclosure, the voltage at the backside conductive layer **198** is

also approximately -15V). Also, in this example, the wells **195** and **196** could be biased to 5V and the well **197** to 0V.

A thing to note is that the well **197** must be narrow and surrounded by a well of a first conductivity type, for example, such as a well **196**. With
 5 said surrounding and a high resistivity substrate, the surrounding well **196** blocks a resistive connection between the well **197** and the backside conductive layer **198**, preventing the well **197** from biasing the backside conductive layer **198**. Again, the distances separating the well **196** and the node **194**, as well as the well **195** and the node **194** must be large
 10 enough for this backside-conductive-layer-biasing scheme to work. CMOS transistors could be placed into the well **195**, and/or the wells **196** and **197**. Typically, the structures of FIGs. 0A and 0B would be placed in the periphery of an image sensor chip. The right side of FIGs. 0A and 0B show an exemplary illustration where a pixel array could start.

15 Moreover, a problem with global shutter imaging with correlated double sampling is that signal acquisition and readout do not take place simultaneously. As a result, a part of the optical signal is lost, and thus, the acquired signal is lower. For example, in a granted US patent US7361877 B2, titled *Pinned-Photodiode Pixel with Global Shutter* , by
 20 inventors R. Daniel McGrath and R. Michael Guidash, 2008, a sense node, a shielded sense node and a floating diffusion are used. First, there is a reset phase that resets the sense nodes and the floating diffusion, followed by integration. Then, an image is captured to the sense node, and after the integration period, is transferred to the shielded sense node.
 25 This is followed by read out of reset and signal values, and the signal that lands on the sensor node during this readout is lost.

There exists a class of applications in which the idea is to emit a light field (usually of a particular wavelength) and measure the reflected light field (that originates from the emitted light) with an image sensor. Light
 30 received by the image sensor that originates from background light (such

as ambient light) is unwanted in the context of light field imaging. One way to improve a Signal-to-Background-Ratio (SBR) is to emit at a specific wavelength of light, and optically filter out other wavelengths before the image sensor. However, the background light on the pass-
5 band of the optical filter remains. Such optical filter also prevents the use of the image sensor as a multi-mode sensor that could also capture a normal intensity image. Another way to improve the SBR is to emit more power to the light field. This increases the power consumption, and eye safety regulations limit the possibility to continuously emit light in such
10 quantities as to significantly improve the SBR. Notably, the eye safety regulations set a maximum acceptable average power and individual pulse power for the emitted light field.

The light field can be uniform or patterned. An example application relying on a patterned light field is a range detector that makes inferences
15 on distances based on a deformation of a reflection of a known pattern of light, as explained in a published US patent application US 2008/0106746, titled *Depth-Varying Light Fields for Three Dimensional Sensing* , by inventors Alexander Shpunt and Zeev Zalevsky, 2011.

SUMMARY

20 The present disclosure seeks to provide an improved pixel element.

The present disclosure also seeks to provide a method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element.

The present disclosure further seeks to provide a system for capturing
25 images.

A further aim of the present disclosure is to provide a solution that overcomes at least partially the problems encountered in the prior art.

In a first aspect, an embodiment of the present disclosure provides a pixel element comprising:

- a semiconductor substrate of a first or second conductivity type, the semiconductor substrate having a front side and a backside, wherein
5 the semiconductor substrate is configured to be exposed to a flux of photons, and to convert the flux of photons to first and second conductivity-type mobile charges;
- a first primary charge-collection node of a first conductivity-type semiconductor material, arranged on the front side of the semiconductor
10 substrate;
- at least one peripheral node of a second conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate, wherein the at least one peripheral node at least partially surrounds the first primary charge-collection node;
- 15 - a circuitry directly connected to the first primary charge-collection node and to the at least one peripheral node, wherein the circuitry comprises:
 - a first switch to connect and disconnect a first reset voltage to/from the first primary charge-collection node;
 - 20 - means to provide a peripheral node voltage to the at least one peripheral node; and
 - a first measurement means to measure an amount of the first conductivity-type mobile charges collected by the first primary charge-collection node;
- 25 - a backside conductive layer arranged on the backside of the semiconductor substrate, configured to collect and conduct the second conductivity-type mobile charges, and configured to be electrically connected to a bias voltage; and
- a first modulating node of the second conductivity-type
30 semiconductor material, wherein the first modulating node is:
 - arranged on the front side of the semiconductor substrate;

- at least partially surrounded by the first primary charge-collection node, which first primary charge-collection node is arranged to provide electrical isolation between the first modulating node and the at least one peripheral node; and
- 5 - electrically connected to a first modulating voltage source, which first modulating voltage source is independent of the peripheral node voltage.

In a second aspect, an embodiment of the present disclosure provides a method for measuring an amount of first conductivity-type mobile
 10 charges associated with a flux of photons received by a pixel element, the pixel element comprising a semiconductor substrate, a first primary charge-collection node, a second primary charge-collection node, a first modulating node, a second modulating node and a circuitry comprising a first switch and a second switch, the method comprising:

- 15 (i) depleting a volume inside of the semiconductor substrate by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate by at least 50 %;
- (ii) providing a first reset voltage (V_{r_a});
- (iii) providing a second reset voltage (V_{r_b});
- 20 (iv) resetting the first primary charge-collection node by:
 - connecting the first primary charge-collection node to the first reset voltage (V_{r_a}) by turning the first switch ON; and
 - disconnecting the first primary charge-collection node from the first reset voltage (V_{r_a}) by turning the first switch OFF;
- 25 (v) resetting a second primary charge-collection node by:
 - connecting the second primary charge-collection node to the second reset voltage (V_{r_b}) by turning a second switch ON; and
 - disconnecting the second primary charge-collection node from the second reset voltage (V_{r_b}) by turning the second switch
- 30 OFF;

(vi) accumulating the first conductivity-type mobile charges to the first and second primary charge-collection nodes during a cycle of:

- decreasing a first charge-collection volume by setting a first modulating voltage (V_{m_a}) to a value that increases a first reverse bias voltage between the first primary charge-collection node and the first modulating node, and increasing a second charge-collection volume by setting a second modulating voltage (V_{m_b}) to a value that decreases a second reverse bias voltage between the second primary charge-collection node and the second modulating node;
- waiting for a first period of time;
- after the first period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_{m_a}) to a value that decreases the first reverse bias voltage between the first primary charge-collection node and the first modulating node, and decreasing the second charge-collection volume by setting the second modulating voltage (V_{m_b}) to a value that increases the second reverse bias voltage between the second primary charge-collection node and the second modulating node;
- and
- waiting for a second period of time; and

(vii) measuring the amount of the first conductivity-type mobile charges accumulated during the cycle of the step (vi) by determining voltage levels (V_{c_a} , V_{c_b}) of the first primary charge-collection node and the second primary charge-collection node.

In a third aspect, an embodiment of the present disclosure provides a method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element, the pixel element comprising a semiconductor substrate, a first primary charge-collection node, a secondary charge-collection node, a first

modulating node, a peripheral node and a circuitry comprising a first switch, the method comprising:

- (a) depleting a volume inside of the semiconductor substrate by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate by at least 50 %;
- (b) providing a first reset voltage (V_r);
- (c) providing a third voltage (V_x);
- (d) resetting the first primary charge-collection node by:
 - connecting the first primary charge-collection node to the first reset voltage (V_r) by turning the first switch ON; and
 - disconnecting the first primary charge-collection node from the first reset voltage (V_r) by turning the first switch OFF;
- (e) accumulating the first conductivity-type mobile charges to the first primary charge-collection node and the secondary charge-collection node during a cycle of:
 - decreasing a first charge-collection volume by setting a first modulating voltage (V_m) to a value that increases a first reverse bias voltage between the first primary charge-collection node and the first modulating node, and increasing a second charge-collection volume by setting the third voltage (V_x) to a value that increases a third reverse bias voltage between the secondary charge-collection node and the peripheral node;
 - waiting for a third period of time;
 - after the third period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_m , V_m) to a value that decreases the first reverse bias voltage between the first primary charge-collection node and the first modulating node, and decreasing the second charge-collection volume by setting the third voltage (V_x) to a value that decreases the third reverse bias voltage between the secondary charge-collection node and the peripheral node; and

- waiting for a fourth period of time; and
 - (f) measuring the amount of the first conductivity-type mobile charges accumulated during the cycle of the step (e) by determining a voltage level (V_c) of the first primary charge-collection node.
- 5 In a fourth aspect, an embodiment of the present disclosure provides a system for capturing images, the system comprising an image sensor, wherein the image sensor comprises a matrix of pixel elements according to the aforementioned first aspect and a controller, the pixel elements being connected to the controller.
- 10 Embodiments of the present disclosure substantially eliminate or at least partially address the aforementioned problems in the prior art, and enable modulation of a quantum efficiency of charge-collection nodes within pixel elements for use in various applications, for example, such as Time-of-Flight (ToF) imaging, light field imaging, High Dynamic Range
- 15 (HDR) imaging, Signal-to-Background Ratio (SBR) improvement and pixel-parallel signal processing.

Additional aspects, advantages, features and objects of the present disclosure would be made apparent from the drawings and the detailed description of the illustrative embodiments construed in conjunction with

20 the appended claims that follow.

It will be appreciated that features of the present disclosure are susceptible to being combined in various combinations without departing from the scope of the present disclosure as defined by the appended claims.

25 BRIEF DESCRIPTION OF THE DRAWINGS

The summary above, as well as the following detailed description of illustrative embodiments, is better understood when read in conjunction with the appended drawings. For the purpose of illustrating the present

disclosure, exemplary constructions of the disclosure are shown in the drawings. However, the present disclosure is not limited to specific methods and instrumentalities disclosed herein. Moreover, those in the art will understand that the drawings are not to scale. Wherever possible,
5 like elements have been indicated by identical numbers.

Embodiments of the present disclosure will now be described, by way of example only, with reference to the following diagrams wherein:

FIGs. 0A-B (Prior Art) show examples of biasing a backside conductive layer;

10 FIGs. 1A-B show a pixel element, while FIG. 1C shows an image sensor made from such pixel elements, according to a first embodiment of the present disclosure;

FIGs. 2A-B show a pixel element, while FIG. 3 shows an image sensor made from such pixel elements, according to a second
15 embodiment of the present disclosure;

FIG. 4A shows a pixel element, according to a third embodiment of the present disclosure;

FIG. 4B shows a pixel element, while FIG. 4C shows an image sensor made from such pixel elements, according to a fourth embodiment
20 of the present disclosure;

FIG. 5A-D show a pixel element, while FIG. 6 shows an image sensor made from such pixel elements, according to a fifth embodiment of the present disclosure;

FIG. 7A-B, 7C, 7D, 7E, 7F, 7G-J, 7K-M, 7N-P and 7Q-R show a pixel
25 element, according to various embodiments of the present disclosure;

FIGs. 8A-F are example illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure;

FIGs. 9A-B are other example illustrations of how the quantum
5 efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure;

FIGs. 10A-E are yet other example illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure;

10 FIGs. 11A-C are still other example illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure;

FIGs. 12A-D are schematic illustrations of a circuitry of a pixel
15 element, in accordance with various embodiments of the present disclosure;

FIG. 13 is a schematic illustration of a circuitry of a pixel element, in accordance with an embodiment of the present disclosure;

FIGs. 14A-B are schematic illustrations of how the collection of
20 charge can be modulated, according to an embodiment of the present disclosure;

FIG. 15 is a schematic illustration of a circuitry of a pixel element, in accordance with an embodiment of the present disclosure;

FIG. 16 is a schematic illustration of an exemplary Pulsed Time-Of-
25 Flight (PTOF) implementation of a system for capturing images, while FIG. 17 is a flowchart depicting the exemplary PTOF implementation, according to an embodiment of the present disclosure;

FIG. 18 is a schematic illustration of an exemplary Global-Shutter (GS) imaging implementation of a system for capturing images, according to an embodiment of the present disclosure;

FIG. 19 is a schematic illustration of an exemplary implementation
5 of a light emitter with a pulsed light field in the aforementioned system, according to an embodiment of the present disclosure;

FIG. 20A is a schematic illustration of multi-mode imaging capabilities of the pixel circuit, in accordance with various embodiments of the present disclosure;

10 FIG. 20B is a schematic illustration of a pixel element with two primary charge-collection nodes and one secondary charge-collection node, in accordance with an embodiment of the present disclosure;

FIG. 21A-D are a schematic illustrations of using tuning implantations, in accordance with an embodiment of the present
15 disclosure and

FIG 22 is an illustration of electric field distribution of the pixel elements, in accordance with an embodiment of the present invention.

In the accompanying drawings, a number is employed to represent an item over which the number is positioned or an item to which the
20 number is adjacent. A number relates to an item identified by a line linking the number to the item. Parts and nodes in the drawings are identified by numberings, wherein similar numbering applies for similar components throughout all the drawings. For example, a peripheral node is identified as **102** in all the drawings.

25 DETAILED DESCRIPTION OF EMBODIMENTS

The following detailed description illustrates embodiments of the present disclosure and ways in which they can be implemented. Although some

modes of carrying out the present disclosure have been disclosed, those skilled in the art would recognize that other embodiments for carrying out or practising the present disclosure are also possible.

In a first aspect, an embodiment of the present disclosure provides a
5 pixel element comprising:

- a semiconductor substrate of a first or second conductivity type, the semiconductor substrate having a front side and a backside, wherein the semiconductor substrate is configured to be exposed to a flux of photons, and to convert the flux of photons to first and second
10 conductivity-type mobile charges;
- a first primary charge-collection node of a first conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate;
- at least one peripheral node of a second conductivity-type
15 semiconductor material, arranged on the front side of the semiconductor substrate, wherein the at least one peripheral node at least partially surrounds the first primary charge-collection node;
- a circuitry directly connected to the first primary charge-collection node and to the at least one peripheral node, wherein the circuitry
20 comprises:
 - a first switch to connect and disconnect a first reset voltage to/from the first primary charge-collection node;
 - means to provide a peripheral node voltage to the at least one peripheral node; and
 - a first measurement means to measure an amount of the first
25 conductivity-type mobile charges collected by the first primary charge-collection node;
- a backside conductive layer arranged on the backside of the semiconductor substrate, configured to collect and conduct the second

conductivity-type mobile charges, and configured to be electrically connected to a bias voltage; and

- a first modulating node of the second conductivity-type semiconductor material, wherein the first modulating node is:
 - 5 - arranged on the front side of the semiconductor substrate;
 - at least partially surrounded by the first primary charge-collection node, which first primary charge-collection node is arranged to provide electrical isolation between the first modulating node and the at least one peripheral node; and
 - 10 - electrically connected to a first modulating voltage source, which first modulating voltage source is independent of the peripheral node voltage.

An example of such a pixel element has been illustrated in conjunction with FIGs. 12A and 1B later.

- 15 Throughout the present disclosure, when the phrase *directly connected* is used, it means that components directly connected to each other (i.e. the connection can carry a direct (DC) current) in practice the direct current connections do not have capacitive connection in between.

It will be appreciated that the first and second conductivity-type semiconductor materials can be either acceptor doped (namely, a p-type semiconductor) or donor doped (namely, an n-type semiconductor). In other words, if the first conductivity-type semiconductor material is an n-type semiconductor, then the second conductivity-type semiconductor material is a p-type semiconductor; and vice versa. As an example, the at least one peripheral node and/or the first modulating node could be formed by way of a doping of the second conductivity-type semiconductor material. Optionally, the at least one peripheral node is implemented in a form of a well into which transistors can be built.

Throughout the present disclosure, the term *semiconductor substrate* refers to a volume that has an original doping of a semiconductor wafer, namely, a volume that is left unchanged during semiconductor processing. Notably, a volume that has been doped, for example, for
5 fabricating charge-collection nodes, modulating nodes and peripheral nodes, is not considered the *semiconductor substrate*.

A first modulating voltage V_m on the first modulating node alters the electric field distribution in a vicinity of the first primary charge-collection node (namely, a substrate volume underneath the first primary charge-
10 collection node, the first modulating node and the at least one peripheral node), thereby modulating a quantum efficiency of the first primary charge-collection node. Throughout the present disclosure, the phrase *modulating the quantum efficiency* refers to changing a size of a charge-collection volume associated with a given charge-collection node.
15 In other words the charge collection volume associated with a given charge-collection node is a volume which has an electric field oriented in a way that it causes first conductivity type mobile charges to drift towards the associated charge collection node. An incident flux of photons land (arrives/hits) on the surface of the image sensor during use (the incident
20 flux is typically quantified by a radiant flux received by a surface per unit area (irradiance)). As the volume of a charge collection node changes, it also affects area of the charge collection volume projected to the surface that is exposed to flux of photons. Therefore, with a constant irradiance, a smaller charge collection volume tends to collect less photogenerated
25 first conductivity type mobile charge carriers, while a larger charge collection volume tends to collect more photogenerated first conductivity type mobile charge carriers. It should be noted that the area of charge collection volume projected to the surface that is exposed to flux of photons is a simplification: the area that is projected to the surface
30 depends on the depth from which the charge collection volume is projected to the surface. Also, photons of small wavelengths tend to get

absorbed closer to the surface than photons of large wavelengths. Indeed it is good to note that term areas of charge collection volumes refers to a simplification, the use of term charge collection areas is useful in describing the operation conceptually.

- 5 Throughout the present disclosure, the term *charge-collection node* refers to a node in a vicinity of which photogenerated charge is collected, while the term *modulating node* refers to a node that is used to facilitate the aforementioned modulation in the quantum efficiency of a corresponding charge-collection node.
- 10 Optionally, the first modulating voltage V_m can be provided via at least two voltages, wherein a first voltage $V_m = V_{hq}$ causes the first primary charge-collection node to be in a high quantum-efficiency state, and a second voltage $V_m = V_{lq}$ causes the first primary charge-collection node to be in a low quantum-efficiency state. Throughout the present
- 15 disclosure, V_{hq} represents a modulating voltage to be used for achieving the high quantum-efficiency state, while V_{lq} represents a modulating voltage to be used for achieving the low quantum-efficiency state.

It will be appreciated that intermediate modulating voltage levels can also be used. Throughout the present disclosure, V_{int_H} represents a
20 modulating voltage to be used for achieving an intermediate high quantum-efficiency state, while V_{int_L} represents a modulating voltage to be used for achieving an intermediate low quantum-efficiency state.

More optionally, the first modulating voltage V_m is set to a continuum of values for an accurate control of the quantum efficiency of the first
25 primary charge-collection node.

It will be appreciated that widths, depths and doping concentrations/profiles of the charge collecting node, the modulating

node and the peripheral node affect the efficiency of the quantum efficiency modulation.

In one embodiment, the pixel element further comprises a secondary charge-collection node of the first conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate.

Throughout the present disclosure, the term *primary charge-collection node* refers to a charge-collection node that at least partially surrounds a modulating node, while the term *secondary charge-collection node* refers to a charge-collection node without a modulating node (i.e., it does not surround any modulating node). In the present disclosure, when a charge-collection node is referred to without specifying whether it is a primary charge-collection node or a secondary charge-collection node, it could be either a primary charge-collection node or a secondary charge-collection node.

In another embodiment, the pixel element further comprises a second primary charge-collection node of the first conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate. Optionally, in such a case, the pixel element further comprises a second modulating node of the second conductivity-type semiconductor material, wherein the second modulating node is:

- arranged on the front side of the semiconductor substrate;
- at least partially surrounded by the second primary charge-collection node, which second primary charge-collection node is arranged to provide electrical isolation between the second modulating node and the at least one peripheral node; and
- electrically connected to a second modulating voltage source, which second modulating voltage source is independent of the peripheral node voltage, and

wherein the circuitry further comprises:

- a second switch to connect and disconnect a second reset voltage to/from the second primary charge-collection node; and
- a second measurement means to measure an amount of the first conductivity-type mobile charges collected by the second primary charge-collection node.

Optionally, a given primary charge-collection node is in a form of a continuous ring. Alternatively, optionally, a given primary charge-collection node has gaps in the ring. The continuous ring may be made into any suitable shape, for example, such as rectangular, rectangular with rounded corners, elliptical, circular and so on.

If there is a gap in the ring of the given primary charge-collection node, then a layer of mobile first conductivity-type charge carriers is optionally introduced in the gap inside the semiconductor material at the semiconductor-insulator interface. The layer of the mobile first conductivity-type charge carriers would be at a same voltage as the primary charge-collection node.

It will be appreciated that relative placement and shapes of modulating nodes and their corresponding charge-collection nodes can be chosen freely, as long as the quantum efficiency of a given primary charge-collection node can be modulated by the modulating voltage V_m at its corresponding modulating node. There is a high enough barrier between the peripheral node and the modulating node, essentially preventing current flow therebetween.

It will be appreciated that the pixel element can comprise a plurality of charge-collection nodes of the first conductivity-type semiconductor material, and is not limited to just two charge-collection nodes, whether both of the charge-collection nodes are primary or one of the charge-collection nodes is secondary. As an example, a given pixel element can comprise three primary charge-collection nodes, for example, as will be

illustrated in conjunction with FIG. 4A later. As another example, a given pixel element can comprise four primary charge-collection nodes, for example, as will be illustrated in conjunction with FIG. 4B later.

In one implementation, the pixel element comprises a plurality of primary charge-collection nodes of the first conductivity-type semiconductor material, wherein each primary charge-collection node is arranged on the front side of the semiconductor substrate. Optionally, in such a case, the pixel element also comprises, for each primary charge-collection node, its corresponding modulating node of the second conductivity-type semiconductor material, wherein the modulating node is:

- arranged on the front side of the semiconductor substrate;
- at least partially surrounded by its corresponding primary charge-collection node, which primary charge-collection node is arranged to provide electrical isolation between the modulating node and the at least one peripheral node; and
- electrically connected to a corresponding modulating voltage source, which modulating voltage source is independent of the peripheral node voltage.

Moreover, in such a case, for each primary charge-collection node, the circuitry further comprises:

- a switch to connect and disconnect a corresponding reset voltage to/from that primary charge-collection node; and
- a measurement means to measure an amount of the first conductivity-type mobile charges collected by that primary charge-collection node.

Additionally, optionally, in such a case (when the pixel element comprises the plurality of charge-collection nodes), the charge-collection nodes and/or modulating nodes are connected to form different groups. Optionally, in this regard, primary charge-collection nodes of a same

group are connected together. In such a case, modulating nodes of such connected primary charge-collection nodes could be controlled together. Similar groupings are optionally applied to all combinations of charge-collection nodes and/or modulating nodes.

- 5 Additionally, optionally, when an image sensor is implemented by way of a matrix of such pixel elements, charge-collection nodes and/or modulating nodes are connected (namely, grouped) between these pixel elements. Such connections can be referred to as inter-pixel connections.

- It will be appreciated that the reset voltages V_r need not be the same for
10 all primary and/or secondary charge-collection nodes. In an extreme case, the reset voltage V_r or the voltage V_x could be different for all primary and/or secondary charge-collection nodes in a given pixel element and/or in a matrix of such pixel elements. Also, the reset voltages can be altered to modulate the quantum efficiency of both
15 primary and secondary charge-collection nodes. This is another way to modulate the quantum efficiency of the primary charge-collection nodes in addition to using corresponding modulating nodes to modulate the quantum efficiency of the primary charge-collection nodes.

- Furthermore, optionally, the circuitry is augmented with a computing
20 circuitry that is capable of controlling the modulating nodes, independently or together with global control signals. The ability to locally determine which primary charge-collection node is in the high quantum-efficiency state plays a role in novel image-capture schemes that utilize sensor-level processing.

- 25 Furthermore, optionally, the pixel element is arranged to receive a flux of photons from the backside of the semiconductor substrate.

It will be appreciated that even when the charge-collection nodes, the peripheral node, the modulating nodes and the circuitry are fabricated onto the front side of the semiconductor substrate, the pixel element can

be illuminated from its backside. Such backside illumination is beneficial in terms of boosting the fill factor and the quantum efficiency. In practice, it is beneficial to thin the semiconductor substrate from the backside in order to obtain more effective backside illumination.

- 5 One way to further improve the quantum efficiency modulation pursuant to embodiments of the present disclosure is to increase the resistivity of the semiconductor substrate by reducing a doping concentration of the semiconductor substrate. A preferred resistivity level depends on, for example, device geometries and other requirements to be decided on a
- 10 case-by-case basis. What is considered a high resistivity substrate depends on the materials and temperature. For silicon at room temperature, a resistivity approximately in a range from 100 Ohm-cm to intrinsic can be considered high resistivity. Preferably, even higher resistivities from 500 Ohm-cm to intrinsic can be used. The quantum
- 15 efficiency modulation is more effective in a high resistivity substrate, because the effect of the modulating voltage V_m is less attenuated by distance in a high resistivity substrate as compared to a low resistivity substrate. In other words, the modulating voltage V_m affects a larger substrate volume in a high resistivity substrate. Thus, electric fields,
- 20 generated due to depletion regions responsible for a drift of charge, extend to a larger volume with a given reverse bias. In general resistivity is a function of doping concentration. For example an acceptor (Boron) doped silicon with $5 \times 10^{13}/\text{cm}^3$ at 300K temperature gives a resistivity of about 270 Ohm-cm. Also, a Boron doped silicon with $1 \times 10^{14}/\text{cm}^3$ at 300K
- 25 temperature gives a resistivity of about 130 Ohm-cm. (notation 1×10^{14} is equivalent with 10 to 14 power i.e. 10^{14})

Optionally, in this regard, the semiconductor substrate is a high resistivity substrate having a doping concentration of at most 1×10^{14} atoms/ cm^3 . More optionally, the semiconductor substrate is a high resistivity

30 substrate having a doping concentration of at most 5×10^{13} atoms/ cm^3 .

It will be appreciated that typical backside-illuminated pixel elements use a semiconductor substrate that is less than 10 micrometres thick. The pixel element pursuant to embodiments of the present disclosure works well with a larger substrate thicknesses of even hundreds of micrometres.

5 Such a semiconductor substrate can be referred to as a thick-thinned substrate. Notably, a thicker substrate (for example, having a thickness in an order of 50 micrometres or more) has many benefits, for example, such as an improved quantum efficiency for near-infrared light and a possibility to do without a support die. With substrate thicknesses of
10 about 50 micrometres or less, a support die (for example, a readout chip) is attached to a CMOS side of the pixel element; otherwise, other means to strengthen the chip physically are needed. This yields a more complex and expensive fabrication in conventional image sensors.

Even if a thinned substrate has a high resistivity, the quantum efficiency
15 modulation allows for an improvement in terms of extending a depleted volume. When the semiconductor substrate is essentially fully depleted, charge is collected from essentially the entire substrate beneath a pixel element. This potentially improves the modulation contrast, because a charge-collection volume that collects the charge (namely, the substrate
20 beneath the pixel) is large, and a charge-collection node that is in the low quantum-efficiency state collects charge only from an immediate vicinity of the charge-collection node.

As mentioned earlier, the backside conductive layer is configured to be electrically connected to the bias voltage (V_{bs}). This helps to fully deplete
25 the semiconductor substrate within the pixel element, and facilitates attainment of a better quantum efficiency and modulation contrast. Essentially the whole semiconductor substrate beneath the pixel element can be depleted by arranging a large enough potential difference between the primary (and/or secondary) charge-collection node(s) and the
30 backside of the pixel element.

As compared to implementations described in a published paper, titled *A 0.13 μm CMOS System-on-Chip for a 512×424 Time-of-Flight Image Sensor With Multi-Frequency Photo-Demodulation up to 130 MHz and 2 GS/s ADC*, by Cyrus S. Bamji et al., IEEE JSSC 2015, embodiments of the present disclosure offer a better modulation contrast, especially where the pixel element is illuminated from the backside, and when the substrate is essentially fully depleted. Embodiments of the present disclosure also offer better quantum efficiency, especially when it comes to detecting near-infrared light. A circuit described in Bamji 15 is also slower, as compared to the circuit pursuant to embodiments of the present disclosure, in terms of moving the collected charge from a given charge-collection node to an integration node because there is a high-resistance region between the charge-collection node and the integration node. In embodiments of the present disclosure, the collection node attracts the photogenerated charge and is directly connected to the readout circuit, and no separate integration node is required. Furthermore, the pixel element pursuant to embodiments of the present disclosure is CMOS compatible in contrast to Bamji 15.

The backside of the semiconductor substrate may be treated in order to make it conductive (see examples below), resulting in the backside conductive layer. As an example, the backside conductive layer may be obtained, for example, by implanting or diffusing a layer of second conductivity-type dopant atoms into the backside of the semiconductor substrate. As another example, the backside conductive layer can be formed by depositing a layer of a second conductivity-type semiconductor material on the backside of the semiconductor substrate.

Optionally, before the formation of the backside conductive layer, the semiconductor substrate is thinned from the backside to a suitable thickness. Optionally, the backside conductive layer is treated, for example and if applicable, by annealing (beneficially, laser annealing).

Optionally, the pixel element is fully CMOS compatible. Additionally, optionally, thinning and steps to fabricate the backside conductive layer are carried out after the CMOS process flow.

Optionally, an anti-reflection treatment is also applied to the backside
5 conductive layer. Very efficient anti-reflection can be obtained when silicon microstructures are coated by charged oxides, for example, as described in a published paper, titled *Near-Unity Quantum Efficiency of Broadband Black Silicon Photodiodes with an Induced Junction* , by Mikko A. Juntunen et al., DOI: 10.1038/NPHOTON.2016.226, which is hereby
10 provided as a reference. Such backside processing steps can be applied to various embodiments of the present disclosure.

It will be appreciated that there are alternative means to obtain the backside conductive layer. As an example, an essentially two-dimensional layer of second conductivity-type mobile charge carriers can be arranged
15 to act as the backside conductive layer. Exemplary means to obtain such a layer of second conductivity-type mobile carriers is to deposit an insulator layer that is suitably charged on the backside of the semiconductor substrate. Such deposition on the backside can be done, for example, using atomic layer deposition. For example,
20 implementations disclosed in the published paper by Juntunen et al., DOI: 10.1038/NPHOTON.2016.226, which is hereby provided as a reference, uses alumina-coated silicon nanostructures on an n-type high-resistivity substrate; alumina is negatively charged, which creates a hole inversion layer inside silicon at the silicon alumina interface.

25 It will be appreciated that when there is a backside conductive layer being used, the semiconductor substrate can be either first conductivity type or second conductivity type, preferably high-resistivity semiconductor material. If there is no backside conductive layer being used, the semiconductor substrate is preferably high-resistivity second

conductivity-type material. This is applicable throughout the present disclosure.

In case the second conductivity type refers to the p-type, then the layer of the second conductivity-type mobile charge carriers can be a hole accumulation layer or a hole inversion layer (both of which can be referred to as a two-dimensional hole gas layer). In case the second conductivity type refers to the n-type, then the layer of the second conductivity-type mobile charge carriers can be an electron accumulation layer or an electron inversion layer (both of which can be referred to as a two-dimensional electron gas layers).

Moreover, some oxides, for example such as alumina and hafnium oxides, are negatively charged when deposited on a silicon substrate, and therefore, attract holes, as explained below:

- on the n-type high-resistivity silicon substrate, alumina or hafnium oxide induces a hole inversion layer inside silicon at the oxide-substrate interface; the hole inversion layer may act as the backside conductive layer and can be biased from the front side of the semiconductor substrate;
- on the p-type high-resistivity silicon substrate, alumina or hafnium oxide induces a hole accumulation layer inside silicon at the oxide-substrate interface; the hole accumulation layer may act as the backside conductive layer and can be biased from the front side of the semiconductor substrate.

The resulting essentially two-dimensional hole gas layer can be used as the backside conductive layer, when the second conductivity-type semiconductor material corresponds to the p-type semiconductor material.

Furthermore, some oxides, for example, such as silicon dioxide, are positively charged when grown or deposited on a silicon substrate, and therefore, attract electrons, as explained below:

- on the n-type high-resistivity silicon substrate, silicon dioxide
5 induces an electron accumulation layer inside silicon at the oxide-substrate interface; the electron accumulation layer may act as the backside conductive layer and can be biased from the front side of the semiconductor substrate;
- on the p-type high-resistivity silicon substrate, silicon dioxide
10 induces an electron inversion layer inside silicon at the oxide-substrate interface; the electron inversion layer may act as the backside conductive layer and can be biased from the front side of the semiconductor substrate.

The resulting essentially two-dimensional electron gas layer can be used
15 as the backside conductive layer, when the second conductivity-type semiconductor material corresponds to the n-type semiconductor material.

For example, if a primary (and/or secondary) charge-collection node is made of an n-type semiconductor material, the backside conductive layer
20 can be created by implanting or diffusing p-type dopant atoms on the backside of the semiconductor substrate, or by depositing a p-type semiconductor material on the backside of the semiconductor substrate, or by depositing or growing a negatively-charged insulator material on the backside of the semiconductor substrate in order to create an
25 essentially two-dimensional hole gas layer. In such a case, the reverse bias between the charge-collection node and the backside conductive layer determines the size of the depleted volume inside the semiconductor substrate. Furthermore, a large enough reverse bias should be applied between the backside conductive layer and the charge-

collection node in order to essentially fully deplete the semiconductor substrate.

As another example, if a primary (and/or secondary) charge-collection node is a p-type semiconductor material, the backside conductive layer
5 can be created by implanting or diffusing n-type dopant atoms on the backside of the semiconductor substrate, or by depositing an n-type semiconductor material on the backside of the semiconductor substrate, or by depositing or growing a positively-charged insulator material on the backside of the semiconductor substrate in order to create an essentially
10 two-dimensional electron gas layer. In such a case, the reverse bias between the charge-collection node and the backside conductive layer determines the size of the depleted volume inside the semiconductor substrate. Furthermore, a large enough reverse bias should be applied between the charge-collection node and the backside conductive layer in
15 order to essentially fully deplete the semiconductor substrate.

If the reverse bias between the (primary and/or secondary) charge-collection node and the backside conductive layer is high enough, the semiconductor substrate becomes essentially fully depleted. By
essentially fully depleted , it is meant that the substrate volume is at
20 least 50% depleted, and more beneficially, is at least 60%, 70%, 80%, 90%, or 100% depleted in an order of preference, wherein 100% is the most preferable value.

Optionally, the backside conductive layer is biased indirectly from the front side through the semiconductor substrate, for example, as
25 explained in the background section of the present disclosure.

Means to arrange the required reverse bias between the charge collection node and the backside conductive layer could be implemented, for example, by way of a circuit located in a peripheral circuitry that controls

the bias voltage V_{bs} through the voltage of a node that is similar to the node **194** of FIGs. 0A and 0B.

Proper control of the bias voltage on the backside conductive layer facilitates a thick (for example, more than ten micrometres), fully-
5 depleted, backside-illuminated pixel element with many benefits, for example, such as a low sensor capacitance, a high quantum efficiency, especially to near-infrared light, a good modulation contrast, a fast charge collection speed, and a 100% fill factor.

An important aspect of embodiments of the present disclosure is to obtain
10 a small primary charge-collection node size, while having a high modulation contrast and collection of charge from the whole pixel element. A higher reverse bias voltage between the charge-collection nodes and the peripheral node allows for smaller sizes of the charge-collection nodes and modulating nodes relative to the whole area of the
15 pixel element. Said higher reverse bias voltage makes it possible to collect photogenerated charge from further away under the peripheral node. If the size of the charge-collection nodes and the modulating nodes is smaller, more charge-collection nodes can be put into a single pixel element and/or the total area of the pixel element can be made smaller.
20 Also, if the size of the charge-collection nodes and the modulating nodes is smaller in relation to the whole area of the pixel element, more transistors can be put into the circuitry of the pixel element of a certain area. This has been elucidated in greater detail in conjunction with FIG. 15.

25 In a second aspect, an embodiment of the present disclosure provides a method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element, the pixel element comprising a semiconductor substrate, a first primary charge-collection node, a second primary charge-collection node, a first

modulating node, a second modulating node and a circuitry comprising a first switch and a second switch, the method comprising:

- (i) depleting a volume inside of the semiconductor substrate by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate by at least 50 %;
- (ii) providing a first reset voltage (V_{r_a});
- (iii) providing a second reset voltage (V_{r_b});
- (iv) resetting the first primary charge-collection node by:
 - connecting the first primary charge-collection node to the first reset voltage (V_{r_a}) by turning the first switch ON; and
 - disconnecting the first primary charge-collection node from the first reset voltage (V_{r_a}) by turning the first switch OFF;
- (v) resetting a second primary charge-collection node by:
 - connecting the second primary charge-collection node to the second reset voltage (V_{r_b}) by turning a second switch ON; and
 - disconnecting the second primary charge-collection node from the second reset voltage (V_{r_b}) by turning the second switch OFF;
- (vi) accumulating the first conductivity-type mobile charges to the first and second primary charge-collection nodes during a cycle of:
 - decreasing a first charge-collection volume by setting a first modulating voltage (V_{m_a}) to a value that increases a first reverse bias voltage between the first primary charge-collection node and the first modulating node, and increasing a second charge-collection volume by setting a second modulating voltage (V_{m_b}) to a value that decreases a second reverse bias voltage between the second primary charge-collection node and the second modulating node;
 - waiting for a first period of time;
 - after the first period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_{m_a})

to a value that decreases the first reverse bias voltage between the first primary charge-collection node and the first modulating node, and decreasing the second charge-collection volume by setting the second modulating voltage (V_{m_b}) to a value that increases the second reverse bias voltage between the second primary charge-collection node and the second modulating node; and

- waiting for a second period of time; and
- (vii) measuring the amount of the first conductivity-type mobile charges accumulated during the cycle of the step (vi) by determining voltage levels (V_{c_a} , V_{c_b}) of the first primary charge-collection node and the second primary charge-collection node.

Optionally, the pixel element further comprises a peripheral node, wherein the method further comprises arranging for the peripheral node to have a potential sufficient for providing at least a 0.6 volt potential barrier to the first conductivity-type charge carriers between the first and the second primary charge-collection nodes when the first and second primary charge-collection nodes are at the first and second reset voltages. In this regard, a peripheral node voltage is applied at the peripheral node. As an example for values of peripheral node voltages for achieving the potential barrier refer to Fig. 14A and Fig14B. In the examples it is assumed that the first conductivity type semiconductor is donor doped (n-type), the reset voltages are 5V, the signal range, i.e., the voltage ranges of the charge collection nodes are from 5V to 3V, peripheral node is at 0V, and backside conductive layer is at -15V.

It will be appreciated that the reset voltages V_{r_a} and V_{r_b} need not be the same for the first and second primary charge-collection nodes. In other words, the first reset voltage V_{r_a} can be different from the second reset voltage V_{r_b} .

Moreover, optionally, the first and second reset voltages are altered to modulate the quantum efficiency of both the first and second primary charge-collection nodes. Notably, this is another way of modulating the quantum efficiency of the first and second primary charge-collection nodes in addition to using the first and second modulating nodes to modulate the quantum efficiency.

In a third aspect, an embodiment of the present disclosure provides a method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element, the pixel element comprising a semiconductor substrate, a first primary charge-collection node, a secondary charge-collection node, a first modulating node, a peripheral node and a circuitry comprising a first switch, the method comprising:

- (a) depleting a volume inside of the semiconductor substrate by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate by at least 50 %;
- (b) providing a first reset voltage (V_r);
- (c) providing a third voltage (V_x);
- (d) resetting the first primary charge-collection node by:
 - connecting the first primary charge-collection node to the first reset voltage (V_r) by turning the first switch ON; and
 - disconnecting the first primary charge-collection node from the first reset voltage (V_r) by turning the first switch OFF;
- (e) accumulating the first conductivity-type mobile charges to the first primary charge-collection node and the secondary charge-collection node during a cycle of:
 - decreasing a first charge-collection volume by setting a first modulating voltage (V_m) to a value that increases a first reverse bias voltage between the first primary charge-collection node and the first modulating node, and increasing a second charge-

collection volume by setting the third voltage (V_x) to a value that increases a third reverse bias voltage between the secondary charge-collection node and the peripheral node;

- waiting for a third period of time;
- 5 - after the third period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_m , V_m) to a value that decreases the first reverse bias voltage between the first primary charge-collection node and the first modulating node, and decreasing the second charge-collection volume by
- 10 setting the third voltage (V_x) to a value that decreases the third reverse bias voltage between the secondary charge-collection node and the peripheral node; and
- waiting for a fourth period of time; and

- (f) measuring the amount of the first conductivity-type mobile charges
- 15 accumulated during the cycle of the step (e) by determining a voltage level (V_c) of the first primary charge-collection node.

Optionally, the method further comprises arranging for the peripheral node to have a potential sufficient for providing at least a 0.6 volt potential barrier to the first conductivity-type charge carriers between the

20 first primary charge-collection node and the secondary charge-collection node when the first primary charge-collection node and the secondary charge-collection node are at the first reset voltage (V_r) and the third voltage (V_x).

In a fourth aspect, an embodiment of the present disclosure provides a

25 system for capturing images, the system comprising an image sensor, wherein the image sensor comprises a matrix of pixel elements according to the aforementioned first aspect and a controller, the pixel elements being connected to the controller.

It will be appreciated that charge-collection nodes of individual pixel

30 elements are isolated from each other, and there is a large enough

potential barrier between the charge-collection nodes of adjacent pixel elements in the matrix.

Optionally, the matrix of pixel elements has local connections between the pixel elements for various purposes, for example, such as pixel-level
5 computation that operates on selected pixel-element signals. As an example, individual pixel elements can have connections to nearest neighbouring pixel elements in cardinal directions. Such connections are not shown in figures of the present disclosure, for the sake of simplicity only.

10 Moreover, if all primary charge-collection nodes and all secondary charge-collection nodes in a neighbourhood of a pixel element (and the entire matrix of pixel elements, in an extreme case) are in the low quantum-efficiency state, there are unwanted leakage currents between peripheral nodes and the semiconductor substrate. Optionally, in order
15 to minimize the leakages, a duration for which all (primary and secondary) charge-collection nodes are in the low quantum-efficiency state can be minimized. Optionally, slightly overlapping voltage pulses are used at the modulating nodes.

Optionally, the quantum efficiency modulation is arranged in a manner
20 that there are enough primary or secondary charge-collection nodes in the high quantum-efficiency state in a pixel neighbourhood at a given time.

Optionally, the system further comprises a light emitter arranged to be directed to a target. Optionally, in this regard, the controller is configured
25 to:

- provide a control signal for the light emitter to emit a pulse of photons at a first moment of time;

- start a measurement to detect a reflected pulse of photons from the target with a first pixel element of the matrix of pixel elements at a second moment of time;
- stop the measurement with the first pixel element at a third
5 moment of time;
- start a measurement to detect the reflected pulse of photons from the target with a second pixel element of the matrix of pixel elements at a fourth moment of time;
- stop the measurement with the second pixel element at a fifth
10 moment of time; and
- calculate a time of flight of the pulse of photons, by comparing an amount of accumulated first conductivity-type mobile charges associated with the reflected pulse of photons in the first pixel element with an amount of accumulated first conductivity-type mobile charges associated
15 with the reflected pulse of photons in the second pixel element.

Additionally or alternatively, optionally, the system further comprises a light emitter configured to emit light pulses at more than one wavelength. Optionally, in this regard, the controller is further configured to adjust modulating voltages (V_m) of modulating nodes of individual pixel
20 elements of the matrix of pixel elements based upon a given wavelength emitted by the light emitter at a given moment of time.

Moreover, optionally, the controller is configured to control the modulating voltages (V_m) based upon pulse duration of the emitted light pulses to:

- 25 - arrange a first charge-collection volume of a first size for a first pulse duration; and
 - arrange a second charge-collection volume of a second size for a second pulse duration,
- wherein the first size is larger than the second size, and the first pulse
30 duration is smaller than the second pulse duration.

It will be appreciated that by modulating the quantum efficiency, it is possible to change the charge-collection volume from which a given pixel element collects photogenerated charges. In effect, pixel boundaries in terms of collecting photogenerated charges (namely, the charge-collection volumes) are not fixed rather they are flexible, i.e., programmable by modulating the quantum efficiency. This will be elucidated in more detail in conjunction with FIGs. 8A-F, 9A-B, 10A-E and 11A-C.

It will be appreciated that flexible (namely, programmable) charge-collection volumes of the pixel elements within the matrix can be used to increase the resolution of the image sensor, for example, by capturing multiple images with different patterns of the modulating voltages V_m (or voltages V_x). It is to be noted here that the voltage V_x can be read out after photogenerated charge has been collected; thus, secondary charge-collection nodes can contribute to the resolution of the image sensor similar to the primary charge-collection nodes.

In one embodiment, the pixel elements of the image sensor have only secondary charge-collection nodes. Such an image sensor has limited capability to modulate the quantum efficiencies of the charge-collection nodes during the integration of the photogenerated charge, but between image frames the quantum efficiencies can be effectively modulated using the voltage V_x after reset. One such example pixel element has been illustrated in conjunction with FIG. 12C.

A key aspect of embodiments of the present disclosure is that modulating the voltages at p-type modulating nodes has a similar effect as that achieved by controlling charge-collection nodes capacitively as described in a granted US patent US6580496 B2. It is to be noted here that in US6580496 B2, capacitive voltage division reduces the amount of quantum efficiency modulation as compared to embodiments of the present disclosure. In other words, embodiments of the present

disclosure have a better modulation contrast, which is a measure of how well the collection of the photogenerated charge can be controlled between charge-collection nodes.

In embodiments of the present disclosure, the modulation is facilitated
5 by modulating the voltages of the modulating nodes; the modulating nodes being low capacitance nodes that are easier to drive with switched voltage sources. In embodiments of the present disclosure, the strength of the quantum efficiency modulation effect can be tuned, for example, with relative widths of the charge-collection nodes and the modulating
10 nodes. The quantum efficiency modulation effect needs to be simulated with physical simulations to verify the best possible operation for a given technology. Additionally, the reset voltages can be used to modulate the quantum efficiency.

Pursuant to embodiments of the present disclosure, the aforementioned
15 system can be implemented in various ways. In one implementation, the aforementioned system is a camera. In another implementation, the aforementioned system is a lidar. The term *lidar* stands for a light detection and ranging system.

In yet another implementation, the system is a Time-of-Flight (ToF)
20 system; in such a case, the system comprises the aforementioned light emitter in addition to the image sensor. The image sensor is operable to collect photogenerated charge into different primary charge-collection nodes depending on the time the charge was photogenerated, and rapidly switch between the primary charge-collection nodes, so as to change the
25 primary charge-collection node that collects the photogenerated charge at a given time. Optionally, the image sensor is fully CMOS compatible.

The modulated image sensor (for example, as shown in FIG. 1A) can be used for ToF applications, by using a required amount of primary charge-collection nodes and the circuitry (for example, as shown in FIG. 15). The

system pursuant to embodiments of the present disclosure can be used for Modulated Time-Of-Flight (MTOF) and Pulsed Time-Of-Flight (PTOF) applications.

It is to be noted that a main difference in the capabilities between primary
5 and secondary charge-collection nodes is the speed of modulation. During one period of signal integration (namely, one frame), the quantum efficiency of a primary charge-collection node can be rapidly and repeatedly switched between different quantum-efficiency states with the aid of the modulating node. This is useful, for example, in ToF
10 applications, where each frame is a result of altering multiple times between the high quantum-efficiency state and the low quantum-efficiency state.

The quantum efficiency of a primary charge-collection node can also be altered with the reset voltage; if the reverse bias voltage after reset is
15 lower after the reset, the quantum efficiency is also lower. The reset is carried out only once per frame so that it is not suitable for modulating the quantum efficiency repeatedly during a single frame. After reset, the reset voltage still connects to the primary charge-collection node through a corresponding capacitor (for example, as will be shown in FIG. 12A-D).
20 This would allow repeated modulation of the quantum efficiency during a single frame. However, such capacitive modulation effect tends to require a high voltage magnitude at the reset node, making such modulation less practical.

The quantum efficiency of a secondary charge-collection node can be
25 altered by a reset voltage; it is thus not well suited for repeated modulations of the quantum efficiency during a single frame. Some proposed implementations of the pixel element (described later) are fine with such modulation in which quantum efficiency remains constant during one frame. For example, a resolution improvement method would
30 work with an image sensor with only secondary charge-collection nodes.

An advantage of this would be a more compact size of the secondary charge-collection node in comparison to a primary charge-collection node.

DETAILED DESCRIPTION OF THE DRAWINGS

5 Referring to FIGs. 1A-B, 2A-B, 4A, 4B, 5A-D, 7A-B, 7C, 7D, 7E, 7F, 7G-J, 7K-M, 7N-P and 7Q-R, illustrated are exemplary implementations of a pixel element **100**, in accordance with various embodiments of the present disclosure. FIGs. 1C, 3, 4C and 6 are schematic illustrations of an image sensor **200** that employs a plurality of pixel elements **100**, in
10 accordance with various embodiments of the present disclosure. It should be understood by a person skilled in the art that these figures include simplified arrangements of the exemplary implementations of the pixel element **100** and the image sensor **200** for the sake of clarity only, which should not unduly limit the scope of the claims herein. Notably, the pixel
15 element **100** is not limited to shapes and arrangements of charge-collection nodes, modulating nodes and surrounding wells shown in these figures. The person skilled in the art will recognize many variations, alternatives, and modifications of embodiments of the present disclosure.

FIG. 1A shows a section view of the pixel element **100**, while FIG. 1B
20 shows a top view of the pixel element **100**, according to a first embodiment of the present disclosure. The cutting plane (A-A) has been shown with arrows labelled with A in FIG. 1B.

With reference to FIGs. 1A and 1B, the pixel element **100** comprises a semiconductor substrate **101** of a first or second conductivity type, a first
25 primary charge-collection node **104**, a peripheral node **102**, a circuitry **107** and a first modulating node **105**. In FIG. 1B, the circuitry **107** is not shown, for the sake of simplicity only.

The semiconductor substrate **101** has a front side and a backside. The semiconductor substrate **101** is configured to be exposed to a flux of photons, and to convert the flux of photons to first and second conductivity-type mobile charges.

- 5 The first primary charge-collection node **104** is composed of a first conductivity-type semiconductor material, while the peripheral node **102** and the first modulating node **105** are composed of a second conductivity-type semiconductor material.

10 The first primary charge-collection node **104**, the peripheral node **102** and the first modulating node **105** are arranged on the front side of the semiconductor substrate **101**. In other words, the first primary charge-collection node **104**, the first modulating node **105** and the peripheral node **102** are fabricated on the semiconductor substrate **101**.

15 The peripheral node **102** at least partially surrounds the first primary charge-collection node **104**. The first modulating node **105** is at least partially surrounded by the first primary charge-collection node **104**. Optionally, the first primary charge-collection node **104** is ring-shaped, for example as shown in FIG. 1B.

20 The first primary charge-collection node **104** is arranged to provide electrical isolation between the first modulating node **105** and the peripheral node **102**.

25 The circuitry **107** is directly connected to the first primary charge-collection node **104**, to the modulating node **105** and to the peripheral node **102**. The circuitry **107** comprises means (not shown) to provide a peripheral node voltage to the peripheral node **102**. The modulating node **105** is electrically connected to a first modulating voltage (V_m) source, which first modulating voltage source is independent of the peripheral node voltage.

In FIG. 1A, V_c represents a voltage at the first primary charge-collection node **104**, while V_m represents a modulating voltage at the first modulating node **105**. The modulating voltage V_m on the first modulating node **105** alters the electric field distribution in a vicinity of
 5 the first primary charge-collection node (namely, a substrate volume underneath the first primary charge-collection node **104**, the first modulating node **105** and the peripheral node **102**), thereby modulating the quantum efficiency of the first primary charge-collection node **104**.

The circuitry **107** further comprises a first switch (not shown) to connect
 10 and disconnect a first reset voltage (V_r) to/from the first primary charge-collection node **104**, and a first measurement means (not shown) to measure an amount of the first conductivity-type mobile charges collected by the first primary charge-collection node **104**.

With reference to FIG. 1C, the image sensor **200** comprises a matrix of
 15 pixel elements **100** and a controller **202** (also referred to as a peripheral circuitry, throughout the present disclosure). Individual pixel elements of the matrix are connected to the controller **202**, via electrical connections **201**, for purposes of input/output operations and biasing.

In FIG. 1C, individual pixel elements within the matrix are denoted by
 20 indexes representing their location in the matrix. As an example, a pixel element in a first row and a first column is denoted by an index **100(1,1)**; a pixel element in the first row and a second column is denoted by an index **100(1,2)**; and so on. Similar naming convention has also been used in later figures.

25 As shown in FIG. 1C, ring-shaped first primary charge-collection nodes electrically isolate corresponding modulating nodes from peripheral nodes. The first primary charge-collection nodes are also isolated from each other. There is a large enough potential barrier between the first primary charge-collection nodes of adjacent pixel elements in the matrix.

The aforementioned first modulating voltage (V_m) source could be provided by way of the circuitry **107** and/or the controller **202**. As mentioned earlier, changing the modulating voltage V_m of a given modulating node **105** alters the quantum efficiency of its surrounding
 5 first primary charge-collection node **104**.

It is to be noted here that in the figures, wherever there are multiple primary charge-collection nodes in a given pixel element, reference numerals have been appended with alphabets to distinguish between different nodes. For example, in FIG. 1A, the first primary charge-
 10 collection node has been denoted by **104**, while its voltage has been noted by V_c . In FIG. 2A, first and second primary charge-collection nodes have been denoted by **104a** and **104b**, whose voltages have been denoted by V_{c_a} and V_{c_b} , respectively. Similar naming convention has been applied to other components. For example, in FIG. 1A, the
 15 modulating node has been denoted by **105**, whose modulating voltage has been denoted by V_m . In FIG. 2A, first and second modulating nodes have been denoted by **105a** and **105b**, whose modulating voltages have been denoted by V_{m_a} and V_{m_b} , respectively.

FIG. 2A shows a section view of the pixel element **100**, while FIG. 2B
 20 shows a top view of the pixel element **100**, according to a second embodiment of the present disclosure. The cutting plane (A-A) has been shown with arrows labelled with A s in FIG. 2B.

With reference to FIGs. 2A and 2B, the pixel element **100** comprises a semiconductor substrate **101** of the first or second conductivity type, a
 25 first primary charge-collection node **104a**, a second primary charge-collection node **104b**, a peripheral node, a circuitry **107**, a first modulating node **105a** and a second modulating node **105b**.

With reference to FIG. 2B, the first and second primary charge-collection nodes **104a** and **104b** are ring-shaped. The first and second primary

charge-collection nodes **104a** and **104b** at least partially surround the first and second modulating nodes **105a** and **105b**, respectively.

The peripheral node is optionally made in a form of a well **102** of a second conductivity-type semiconductor material, as shown in FIG. 2A. Between
 5 the first and second primary charge-collection nodes **104a** and **104b**, there is a region **106** of another second conductivity-type semiconductor material, which may be same as or different from the second conductivity-type semiconductor material of the well **102** in terms of, for example, doping concentration, thickness, and so forth. The well **102** and
 10 the region **106** are connected together to form the peripheral node (hereinafter referred to as the *peripheral node 102*, for the sake of convenience).

The first and second primary charge-collection nodes **104a** and **104b** electrically isolate the first and second modulating nodes **105a** and **105b**
 15 from the peripheral node **102**, respectively. The first and second primary charge-collection nodes **104a** and **104b** are also electrically isolated from each other. Such isolation is achieved when there is a large enough potential barrier between the first and second primary charge-collection nodes **104a** and **104b** essentially preventing current flow therebetween.
 20 This can be accomplished, for example, with the second conductivity-type semiconductor material of the region **106**.

Optionally, the circuitry **107** is placed in the well **102**. As an example, at least one first conductivity-type Metal-Oxide-Semiconductor Field-Effect Transistor (MOSFET) can be built on the well **102** of the second
 25 conductivity-type semiconductor material.

Alternatively, optionally, a deep well is formed, for example, by a combination of the second conductivity-type semiconductor material of the well **102** with yet another second conductivity-type semiconductor material of a region **1020**. Optionally, in such a case, a well **103** of a first

conductivity-type semiconductor material is built on the deep well, and at least one second conductivity-type MOSFET is built into the well **103**.

Likewise, other circuit components (for example, such as capacitors, resistors and the like) that have been employed in the circuitry **107**
5 (based upon a semiconductor fabrication technology used for fabrication) can be built into the well **102**, the deep well **102/1020** and/or the well **103**.

With reference to FIG. 3, the image sensor **200** comprises a matrix of pixel elements **100** of FIG. 2A-B and a controller (not shown). Individual
10 pixel elements of the matrix are connected to the controller, via electrical connections.

In this embodiment, the first and second primary charge-collection nodes **104a** and **104b** within a same pixel element **100** are closer to each other than to adjacent primary charge-collection nodes of neighbouring pixel
15 elements **100**.

FIG. 4A shows a top view of the pixel element **100**, according to a third embodiment of the present disclosure. In FIG. 4A, the pixel element **100** comprises three primary charge-collection nodes **104a**, **104b** and **104c** arranged in a side-by-side manner.

20 FIG. 4B shows a top view of the pixel element **100**, according to a fourth embodiment of the present disclosure. In FIG. 4A, the pixel element **100** comprises four primary charge-collection nodes **104a**, **104b**, **104c** and **104d** arranged in a two-by-two array.

With reference to FIG. 4C, the image sensor **200** comprises a matrix of
25 pixel elements **100** of FIG. 4B and a controller (not shown). Individual pixel elements of the matrix are connected to the controller, via electrical connections.

Optionally, the primary charge-collection nodes and/or modulating nodes are connected to form different groups. As an example, in Fig. 4B, the primary charge-collection nodes **104a** and **104c** could be connected together, while the primary charge-collection nodes **104b** and **104d** could be connected together. In such a case, modulating nodes of such connected primary charge-collection nodes could be controlled together to form a group.

FIG. 5A shows a top view of the pixel element **100**, FIG. 5B, 5C and 5D show section views of the pixel element **100** for cutting planes A-A, C-C and B-B, respectively, according to a fifth embodiment of the present disclosure.

With reference to FIGs. 5A-D, the pixel element **100** comprises a semiconductor substrate **101** of a first or second conductivity type, a first primary charge-collection node **104**, a first modulating node **105**, a secondary charge-collection node **180**, a peripheral node **102** and a circuitry **107**. The secondary charge-collection node **180** does not have a corresponding modulating node (i.e., it does not surround any modulating node). The secondary charge-collection node **180** is made of a first conductivity-type semiconductor material.

In FIGs. 5B-D, V_c represents a voltage at the first primary charge collection node **104**, V_m represents a modulating voltage at the first modulating node **105**, and V_x represents a voltage at the secondary charge-collection node **180**. The modulating voltage V_m on the first modulating node **105** alters the electric field distribution in a vicinity of the first primary charge-collection node **104**, thereby modulating the quantum efficiency of the first primary charge-collection node **104**. Likewise, the quantum efficiency of the secondary charge-collection node **180** can be altered with the voltage V_x . The secondary charge-collection node **180** is useful in attaining, for example, the global shutter

functionality and an improvement in a resolution of a captured image, as will be described later in the present disclosure.

With reference to FIG. 6, the image sensor **200** comprises a matrix of pixel elements **100** of FIGs. 5A-D and a controller (not shown). Individual
5 pixel elements of the matrix are connected to the controller, via electrical connections.

FIG. 6 is an exemplary illustration of how primary and secondary charge-collection nodes **104** and **180** can be located with respect to each other in one embodiment. It will be appreciated that there can be multiple
10 primary charge-collection nodes and/or secondary charge-collection nodes arranged and placed in various possible ways in a pixel element.

FIG. 7A shows a section view of the pixel element **100**, according to a sixth embodiment of the present disclosure. The pixel element **100** comprises a semiconductor substrate **101** of a first or second conductivity
15 type, a first primary charge-collection node **104**, a first modulating node **105**, a peripheral node **102**, a circuitry **107** and a tuning implantation **125**. The tuning implantation **125** is implanted into the semiconductor substrate **101**. It will be appreciated that there can be multiple layers of such tuning implantations, and they can be made of either a first
20 conductivity-type semiconductor material or a second conductivity-type semiconductor material.

The purpose of a tuning implantation is to help the charge collection for a larger volume, and, for example, to help in collection of the charge from a particular depth in the semiconductor substrate. This is potentially
25 useful, for example, in making a primary or secondary charge-collection node sensitive to a particular wavelength, and less sensitive to other(s).

FIG. 7B shows the pixel element **100** with a structured tuning implantation **126**.

Fig. 7A and 7B also highlight that there can be a gap between the peripheral node **102**, the primary charge-collection node **104** and the modulating node **105**; said gap may be required, for example, due to reasons of semiconductor fabrication or electrical isolation.

5 Fig. 7C shows a section view of the pixel element **100**, according to a seventh embodiment of the present disclosure. In FIG. 7C, the pixel element **100** comprises a Shallow Trench Isolation (STI) **124** that is used between implantations. The use of such STI may be required, for example, due to reasons of semiconductor fabrication or electrical
10 isolation, and in order to minimize parasitic capacitance between different nodes of the pixel element.

FIG. 7D shows a section view of the pixel element **100**, according to an eighth embodiment of the present disclosure. In this implementation, gates **123** (for example, such as polysilicon gates) are used between the
15 primary charge-collection node **104** and the modulating node **105** to reduce leakage currents therebetween. The gates **123** induce a field effect that lowers the conductance between the charge-collection node **104** and the modulating node **105**.

The gates **123** are connected to the modulating node **105** (which is at
20 the modulating voltage V_m). However, the gates **123** could also be controlled by dedicated voltage sources or other voltage nodes in the circuitry **107** or a peripheral circuitry (for example, such as the controller **202**).

Also shown in Fig. 7D is an optional STI **124** that may be used at the
25 boundaries of the semiconductor materials to improve electrical isolation and to reduce, for example to minimize, parasitic capacitance. It will be appreciated that a gate with a controlled voltage can be used in place of an STI between any implants or nodes.

Optionally, the image sensor **200** is fabricated as a single chip, wherein the charge-collection nodes **104** and/or **180**, the circuitry **107** and the controller **202** are all located on the same semiconductor substrate **101**.

Alternatively, optionally, different parts of the image sensor **200** are
 5 divided into different semiconductor substrates (chips) that are electrically connected to each other, wherein said semiconductor substrates can be made of silicon or other semiconductor materials. It will be appreciated that while the image sensor **200** is readily applicable in silicon-based realizations, any other semiconductor material, for
 10 example, such as compound semiconductors like GaAs, InP, and Germanium-based semiconductors can also be used.

A part or an entirety of the circuitry **107** and/or the controller **202** can reside on separate substrates, wherein chip-to-chip connections within the circuitry **107** and to the charge-collection nodes **104** and/or **180**, the
 15 modulating nodes **105** and peripheral node **102** may be needed. In this case, the charge-collection nodes **104** and/or **180**, the modulating nodes **105**, the peripheral node **102** and possibly a part of the circuitry **107** along with the controller **202** are located in a chip denoted as a *collection chip* , while some or all of the circuitry **107** is located in another chip
 20 denoted as a *readout chip* or multiple other chips. Said readout chip may also be called a readout integrated circuit. A benefit of using a separate collection chip and readout chip(s) is that optimal technology can be used for both the collection chip and the readout chip(s).

Furthermore, while the circuitry **107** may comprise resources (for
 25 example, such as transistors, capacitors and the like) that are associated with a particular charge-collection node, it will be appreciated that some resources of the circuitry **107** may be shared with other charge-collection nodes within a given pixel element. Additionally, some resources of the circuitry **107** of a given pixel element may be shared with other pixel

elements. Such sharing of resources is not shown in the figures, for the sake of simplicity only.

FIG. 7E shows a section view of the pixel element **100**, according to a ninth embodiment of the present disclosure. The pixel element **100**
 5 further comprises a backside conductive layer **108**.

The backside conductive layer **108** is arranged on the backside of the semiconductor substrate **101**. The backside conductive layer **108** is configured to collect and conduct the second conductivity-type mobile charges.

10 The backside conductive layer **108** is configured to be electrically connected to a bias voltage (V_{bs}). This helps to fully deplete the semiconductor substrate **101** within the pixel element **100**, and facilitates attainment of a better quantum efficiency and modulation contrast.

15 FIG. 7F shows a section view of the pixel element **100**, according to a tenth embodiment of the present disclosure. In Fig. 7F, the modulating node **105** extends deeper into the semiconductor substrate **101**. In principle, it is possible to fabricate components (for example, such as transistors) into the modulating node **105**, if the volume of the
 20 modulating node **105** is large enough.

Notably, widths, depths and doping concentrations/profiles of the charge collecting nodes **104** and **108**, the modulating nodes **105** and the peripheral node **102** affect the efficiency of the quantum efficiency modulation.

25 FIG. 7G shows a top view of the pixel element **100**, FIGs. 7H and 7J show section views of the pixel element **100** for cutting planes A-A and B-B, respectively, according to an eleventh embodiment of the present

disclosure. In this embodiment, the primary charge-collection node **104** has a gap in its ring form.

Instead of having the primary charge-collection node **104** made solely of a first conductivity-type semiconductor material, the primary charge-
 5 collection node **104** comprises a region **1040** of a first conductivity-type semiconductor material and a region **1041** of an insulator material that is charged with second conductivity-type charges.

FIG. 7H and 7J highlight that a layer of mobile first conductivity-type charge carriers **190** is formed inside the semiconductor material at the
 10 semiconductor-insulator interface.

FIG. 7K shows a top view of the pixel element **100**, FIGs. 7L and 7M show section views of the pixel element **100** for cutting planes A-A and B-B, respectively, according to a twelfth embodiment of the present disclosure. The primary charge-collection node **104** comprises a region
 15 **1040** of a first conductivity-type semiconductor material, a region **1042** of an insulator material, and a region **1043** of a conductor material, wherein the region **1043** is formed over the region **1042**. The region **1043** can be connected to the region **1040**, or be controlled independently.

20 FIG. 7L and 7M highlight that the conductor-insulator-semiconductor stack forms a gate structure, where a voltage at the conductor **1043** can be arranged to a voltage level that results in the formation of a layer of mobile first conductivity-type charge carriers **190** underneath the gate structure.

25 FIG. 7N shows a top view of the pixel element **100**, FIG. 7P shows a section view of the pixel element **100** for a cutting planes A-A, according to a thirteenth embodiment of the present disclosure. The modulating node comprises a region **1050** of a conductor material and a region **1051**

of an insulator material, wherein the region **1050** is formed over the region **1051**.

FIG. 7P highlights that a stack of conductor insulator-semiconductor forms a gate that can induce a layer of mobile charge carriers in the semiconductor beneath the insulator of the region **1051**, when a suitable voltage is applied to the conductor of the region **1050**. Controlling the voltage of the region **1050** has a similar effect as controlling a modulation node that is formed by a second conductivity-type semiconductor.

FIG. 7P also shows an alternative embodiment for the backside conductive layer, which is shown as a layer **191** of mobile second conductivity-type charge carriers formed inside the semiconductor material at a semiconductor-insulator interface between the semiconductor substrate **101** and an insulator layer **1080**. The insulator layer **1080** is made of an insulator material that comprises first conductivity-type charges.

FIG. 7Q shows a top view of the pixel element **100**, FIG. 7R shows a section view of the pixel element **100** for a cutting planes A-A, according to a fourteenth embodiment of the present disclosure. The peripheral node is denoted by **1020**, and is made of a conductor forming a Schottky diode with the underlying semiconductor material, wherein the Schottky diode comprises a Schottky barrier for mobile first conductivity-type charge carriers. The primary charge-collection node is denoted by **1044**, and is made of a conductor forming an Ohmic contact with the underlying semiconductor material for mobile first conductivity-type charge carriers. The modulating node is denoted by **1052**, and is made of a conductor material forming a Schottky diode with the underlying semiconductor material, wherein the Schottky diode comprises a Schottky barrier for first conductivity-type charge carriers.

FIG. 7R also shows an alternative embodiment for the backside conductive layer, which is shown as a layer **1081** of a conductor material forming a Schottky diode with the semiconductor substrate **101**, wherein the Schottky diode comprises a Schottky barrier for mobile first conductivity-type charge carriers.

It will be appreciated that various implementation techniques illustrated in conjunction with FIGs. 7A to 7R are optional and merely examples; any combination of said techniques may or may not be used in various embodiments of the present disclosure.

- FIGs. 8A-F are some example schematic illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure. FIGs. 8A-F show section views of a portion of a matrix of pixel elements, in accordance with an embodiment of the present disclosure.
- Assume the matrix of pixel elements with $i=[1,M]$ rows and $j=[1,N]$ columns, wherein M and N are positive integers 3 and 6, respectively. A particular pixel element within the matrix is identified with $100(i,j)$.

FIG. 8A shows a section view of a portion of a second row of the matrix, wherein said portion comprises pixel elements **100(2,2)**, **100(2,3)**, **100(2,4)** and **100(2,5)** of the matrix. Therefore, all pixel elements shown in FIG. 8A are surrounded by their neighbouring pixel elements within the matrix, and therefore, have a well-defined neighbourhood. Furthermore, assume there is a high enough reverse bias between the backside conductive layer **108** and the primary charge-collection nodes **104** of the pixel elements to essentially fully deplete the semiconductor substrate **101** within the whole pixel element volume. It will be appreciated that the semiconductor substrate **101** being essentially fully depleted is not necessarily required for an image sensor to work, but the illustration in FIGs. 8A-F assumes said condition.

Next, for illustration purposes only, there will now be considered an illustrative example of the relative magnitudes of the voltages. In the illustrative examples, the first conductivity-type semiconductor material is set to the n-type semiconductor (namely, donor impurities added to a semiconductor); said setting of the first conductivity-type semiconductor material allows use of both magnitudes of potential differences and signs of potential differences for purposes of illustration. The voltage of the peripheral node **102** is denoted as the ground potential (namely, zero volts) with respect to which other voltages are referred to. Exemplary voltages could be such that the backside conductive layer **108** is at -15 V, the peripheral node **102** is at 0 V, the voltage on the charge-collection nodes **104** are allowed to be in a range between 5 V and 3 V.

In FIGs. 8A-F, $V_c = V_r$; V_r is the reset voltage and in this example, is 5 V; the charge-collection nodes **104** are at the voltage V_c at the start of the integration. In this case, a potential difference between V_c and V_{bs} is between 18 V and 20 V; such a potential difference between the charge-collection nodes **104** and the backside conductive layer **108** is typically enough to essentially fully deplete a relatively thick-thinned high-resistivity substrate. The actual reverse bias voltage between the charge-collection nodes **104** (V_{bs}) that is large enough to essentially fully deplete the semiconductor substrate **101** depends on the substrate material, a substrate doping level and a thickness of the semiconductor substrate **101**. Said reverse bias voltage can be found out, for example, by physical simulations. The modulating voltages V_m of the modulating nodes **105** should be below the voltages of the primary charge-collection nodes **104**, in order to avoid forward biasing the p-n junctions between the primary charge-collection nodes **104** and the modulating nodes **105**. In this illustrative example, the modulating voltages V_m corresponding to the high quantum-efficiency state and the low quantum-efficiency state could be in an order of $V_{hq} = 2.5$ V and $V_{lq} = 0$ V, respectively.

The example implementation uses also intermediate modulating voltages, which could in the illustrative example be a voltage $V_{int_H}=1.25V$ that yields the intermediate high quantum-efficiency state and a voltage $V_{int_L}=0.75V$ that yields the intermediate low quantum-efficiency state, respectively.

FIG. 8B shows a first example case, where all the pixel elements in the matrix have a V_{hq} in their modulating nodes **105**; in other words, the pixel elements are in the high quantum-efficiency state. The arrows **145** show electric field lines in the semiconductor substrate **101**. The primary charge-collection node **104** of the pixel element **100(2,2)** collects charge from a region depicted by the thick dashed lines **140** and **141**; the primary charge-collection node **104** of the pixel element **100(2,3)** collects charge from a region depicted by the thick dashed lines **141** and **142**; the primary charge-collection node **104** of the pixel element **100(2,4)** collects charge from a region depicted by the thick dashed lines **142** and **143**; the primary charge-collection node **104** of the pixel element **100(2,5)** collects charge from a region depicted by the thick dashed lines **143** and **144**. The thick dashed lines **140**, **141**, **142** and **143** in Fig. 8B represent boundaries of charge collection volumes between adjacent pixels. It should be noted that in Fig. 8B while approaching a boundary of a charge collection volume the electric field component that is perpendicular to the boundary of charge collection volume reduces smoothly towards the boundary and reaches zero at the boundary. There is a vertical electric field in the charge collection volume boundary to either **102** or **108**. It should be noted that in a more detailed figure there would also be illustrations of electric field lines running between the peripheral node **102** and the charge collection node, in a similar fashion as there are electric field lines between the modulating node **105** and the charge collection node. These are not drawn in the figure for clarity sake.

FIG. 8C shows a second example case, where odd columns of the pixel elements have V_{hq} in their modulating nodes **105** (namely, are in the high quantum-efficiency state) and even columns of the pixel elements have a V_{int_H} in their modulating nodes **105** (namely, are in the intermediate high quantum-efficiency state). The electric field lines (depicted by the arrows **145**) have changed according to the changes in the modulating voltages; the thick dashed lines **140** and **141**, as well as **142** and **143** have moved closer to each other and bent. It is to be noted here that the thick dashed line **144** has moved towards an adjacent pixel element **100(2,6)** and is not shown in FIG. 8C. As a result of the changes in the modulating voltages, the primary charge-collection nodes **104** in the even columns collect photogenerated charge from a narrower charge-collection volume as compared to FIG. 8B. On the other hand, the primary charge-collection nodes **104** in the odd columns collect charge from a wider charge-collection volume as compared to FIG. 8B.

FIG. 8D shows a third example case, where the odd columns of the pixel elements have V_{hq} in their modulating nodes **105** (namely, are in the high quantum-efficiency state) and the even columns of the pixel elements have a V_{int_L} in their modulating nodes **105** (namely, are in the intermediate low quantum-efficiency state). The thick dashed lines **140** and **141**, as well as **142** and **143** are closer to each other as compared to FIG. 8C. Said lines are on top of each other near the backside of the semiconductor substrate **101**. As a result, the primary charge-collection nodes **104** in the even columns do not collect charge that is photogenerated in the vicinity of the backside. This effectively means that short wavelengths that are absorbed near the backside are not captured by the even columns of the pixel elements. Thus, spectrally-selective imaging is possible; in the example of FIG. 8D, the primary charge-collection nodes **104** in the even columns absorb light that has in effect been long-pass filtered by the pixel elements in the odd columns.

FIG. 8E shows a fourth example case, where the odd columns of the pixel elements have V_{hq} in their modulating nodes **105** (namely, are in the high quantum-efficiency state) and the even columns of the pixel elements have a V_{lq} in their modulating nodes **105** (namely, are in the low quantum-efficiency state). In this case, the pixel elements in the even columns collect charge only from the immediate vicinity of their primary charge-collection nodes **104** as indicated by the thick dashed lines **140**, **141**, **142** and **143**.

FIG. 8F shows a fifth example case, where:

- the pixel elements 100(i,1) have $V_m = V_{hq}$,
- the pixel elements 100(i,2) have $V_m = V_{lq}$,
- the pixel elements 100(i,3) have $V_m = V_{hq}$,
- the pixel elements 100(i,4) have $V_m = V_{hq}$,
- the pixel elements 100(i,5) have $V_m = V_{int_H}$, and
- the pixel elements 100(i,6) have $V_m = V_{hq}$.

This example case illustrates that different combinations of modulating voltages are possible within the matrix of pixel elements. It will be appreciated that by modulating the quantum efficiency, it is possible to change the charge-collection volume from which a pixel element collects photogenerated charges. In effect, the pixel boundaries in terms of collecting photogenerated charges are not fixed rather they are flexible, i.e., programmable by modulating the quantum efficiency.

The exemplary illustrations in FIGs. 8A-F were drawn for an example embodiment in which each pixel element comprises a single primary charge-collection node. It will be appreciated that the quantum efficiency can be modulated in a similar manner in various other embodiments of the present disclosure. The principle described in FIGs. 8A-F can be extended to pixel elements with multiple primary and/or secondary charge-collection nodes, and to image sensors comprising matrices of a higher dimension. Moreover, in an example embodiment in which each

pixel element comprises a secondary charge-collection node in addition to the primary charge-collection node, the voltage V_x of the secondary charge-collection node could be used to alter the quantum efficiency of the secondary charge-collection node.

- 5 Fig. 21A is an illustration of an another example of using tuning implantations. An implant **1251** is of second conductivity type semiconductor material, and an implant **1250** is of first conductivity type semiconductor material. The implants **1251** and **1250** might be lightly doped so that said implants are fully depleted when the sensor is
- 10 operated. The implant **1251** aims to improve the modulation, while the implant **1250** helps steer mobile first conductivity type charges towards the charge collection node. These implants can also be used individually, for example only **1250** or only **1251**, while their combination might result for improved modulation of quantum efficiency.
- 15 Fig. 21B is an illustration of an example of using tuning implantations with a pixel element with one primary and one secondary charge collection node. There is implant of second conductivity type semiconductor material **1251**, as well as implant of first conductivity type semiconductor material **1253**. Furthermore, there is implant of second
- 20 conductivity type semiconductor material **1254** below the secondary charge collection node **180**. The tuning implants helps steer charge to primary **104** and secondary **180** charge collection nodes and facilitate the quantum efficiency modulation of said charge collection nodes. The implants **1251**, **1253** and **1254** can be lightly doped so that said
- 25 implants are fully depleted when the sensor is operated.

Fig. 21C is an illustration of an example of using tuning implantations with a pixel element with two primary charge collection nodes. The situation is analogous to that of using two pixel elements of Fig. 21A.

Fig. 21D is an illustration of an example of using tuning implantations with a pixel element with two primary charge collection nodes. The situation is analogous to that of using two pixel elements of Fig. 21C, except that now the tuning implantation **1252** is structured so that it
 5 does not extend all the way to the edge of the pixel element. This helps separate the charge collection volumes of one pixel element from charge collection nodes of adjacent pixel elements. The implants **1251** and **1252** can be lightly doped so that said implants are fully depleted when the sensor is operated.

10 The described tuning implantations are illustrative examples and can be used in different combinations.

Fig. 22 provides a more detailed illustration of the electric field distribution of the pixel elements and biasing conditions of Fig. 8B. The thick dashed lines **140**, **141** and **142** of Fig. 22 represent boundaries of
 15 charge collection volumes between adjacent pixels. It should be noted that similarly to Fig. 8B while approaching a boundary of a charge collection volume the electric field component that is perpendicular to the boundary of charge collection volume reduces smoothly towards the boundary and reaches zero at the boundary. In Fig. 22 the electric field
 20 lines are drawn to illustrate that the second conductivity type mobile charges which are generated at the charge boundary end up either at the peripheral node **102** or at the backside conductive layer **108**. That is because there is a vertical electric field in the charge collection volume boundary to either **102** or **108**. In Fig. 22 are also illustrated electric field
 25 lines running between the peripheral node **102** and the charge collection node (these are not illustrated in Fig. 8B, 8C, 8D, 8E, and 8F for clarity reasons) in a similar fashion as there are electric field lines between the modulating node **105** and the charge collection node.

As a note to Fig. 8B, Figs 8C, 8D, 8E, and 8F show the electric field lines only roughly, but the boundaries between charge collection volumes behave qualitatively as illustrated in Figs. 8B, 8C, 8D, 8E, and 8F.

FIGs. 9A-B are other example illustrations of how the quantum efficiency
 5 of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure. FIGs. 9A-B show top views of a portion of a matrix of pixel elements, in accordance with an embodiment of the present disclosure.

For illustration purposes only, there will now be considered the matrix of
 10 pixel elements with $i=[1,M]$ rows and $j=[1,N]$ columns, wherein M and N are positive integers 3 and 10, respectively. Said portion comprises pixel elements **100(2,2)**, **100(2,3)**, **100(2,4)**, **100(2,5)**, **100(2,6)**, **100(2,7)**, **100(2,8)** and **100(2,9)** of the matrix.

Primary charge-collection nodes of the pixel elements **100(2,2)**,
 15 **100(2,3)**, **100(2,4)**, **100(2,5)**, **100(2,6)**, **100(2,7)**, **100(2,8)** and **100(2,9)** collect photogenerated charge from charge-collection volumes beneath areas **150**, **151**, **152**, **153**, **154**, **155**, **156** and **157**, respectively. It will be appreciated that the areas **150**, **151**, **152**, **153**, **154**, **155**, **156** and **157** are merely indicative. As is observable in FIGs.
 20 8A-F, a charge-collection volume from which a given primary charge-collection node collects photogenerated charge depends on the depth at which the photogeneration takes place.

The primary charge-collection nodes, modulating nodes and peripheral nodes of the pixel elements **100(2,2)**, **100(2,3)**, **100(2,4)**, **100(2,5)**,
 25 **100(2,6)**, **100(2,7)**, **100(2,8)** and **100(2,9)** shown in FIGs. 9A-B are not labelled, for the sake of clarity only.

FIG. 9A shows an example case, where:
 the pixel elements 100(i,1) have $V_m=V_{hq}$,

- the pixel elements 100(i,2) have $V_m = V_{hq}$,
the pixel elements 100(i,3) have $V_m = V_{int_H}$,
the pixel elements 100(i,4) have $V_m = V_{hq}$,
the pixel elements 100(i,5) have $V_m = V_{hq}$,
5 the pixel elements 100(i,6) have $V_m = V_{lq}$,
the pixel elements 100(i,7) have $V_m = V_{hq}$,
the pixel elements 100(i,8) have $V_m = V_{hq}$,
the pixel elements 100(i,9) have $V_m = V_{hq}$, and
the pixel elements 100(i,10) have $V_m = V_{hq}$.
- 10 It will be appreciated that boundaries of the volumes in terms of collecting photogenerated charge (namely, the charge-collection volumes) can be changed electrically with the modulating voltages.

FIG. 9B shows another example case, where:

- the pixel elements 100(i,j) whose j satisfies $\text{mod}(j,3)=1$ have $V_m = V_{int_H}$
15 (the intermediate high quantum-efficiency state), while other pixel elements 100(i,j) whose j satisfies $\text{mod}(j,3)=0$ and $\text{mod}(j,3)=2$ have $V_m = V_{hq}$ (the high quantum-efficiency state).

- It is to be noted that the notation of the modulo operation $\text{mod}(j,3)$ is equivalent to $j \bmod 3$. It can be observed from FIG. 9B that in this
20 example case, the pixel elements 100(2,j) whose $\text{mod}(j,3)=1$ collect photogenerated charge from about one-third of the actual width of the pixel element, while photogenerated charge from remaining two-third of the pixel element are collected by adjacent pixel elements 100(2,j) whose $\text{mod}(j,3)=0$ or $\text{mod}(j,3)=2$.

- 25 Moreover, measurements of photogenerated charge in various cases, for example, wherein:

Case A: all pixel elements have $V_m = V_{hq}$,

Case B: pixel elements satisfying $\text{mod}(j,3)=1$ have $V_m = V_{int_H}$,

Case C: pixel elements satisfying $\text{mod}(j,3)=2$ have $V_m=V_{\text{int_H}}$, and

Case D: pixel elements satisfying $\text{mod}(j,3)=0$ have $V_m=V_{\text{int_H}}$,

can be used to divide each pixel element vertically into three parts. Thus, with these four measurements, a vertical resolution of the matrix can be
 5 three times the number of pixel elements in a row. It will be appreciated that the abovementioned cases are merely an example for illustrating the principle behind the modulating voltages and their patterns. Different combinations of modulating voltages and their patterns can be used to divide a pixel element into parts, resulting in an increased resolution.

10 FIGs. 10A-B are yet other example illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure. FIGs. 10A-B show top views of a portion of a matrix of pixel elements, in accordance with an embodiment of the present disclosure. For illustration
 15 purposes only, there will now be considered the matrix of pixel elements with $i=[1,M]$ rows and $j=[1,N]$ columns, wherein M and N are positive integers 5 and 5, respectively.

With reference to FIG. 10A, pixel elements **100(3,3)**, **100(1,2)**, **100(2,5)**, **100(5,4)** and **100(4,1)** have $V_m=V_{\text{int_H}}$, while other pixel
 20 elements have $V_m=V_{\text{hq}}$. Primary charge-collection nodes of the pixel elements **100(3,2)**, **100(2,3)**, **100(3,4)**, **100(4,3)** and **100(3,3)** collect photogenerated charge from charge-collection volumes beneath areas (shown enclosed by thick lines) **171**, **172**, **173**, **174** and **175**.

With reference to FIG. 10B, all of the pixel elements have $V_m=V_{\text{hq}}$. As a
 25 result, the charge-collection volumes have become symmetric.

In FIG. 10C, the pixel element **100(3,3)** has been split into five areas **1710**, **1720**, **1730**, **1740**, **175**.

FIG. 10D shows how the number of photogenerated charges per unit area and time can be computed for charge-collection volumes underneath the areas **1710**, **1720**, **1730**, **1740** and **175**.

With reference to FIG. 10D, the area **171** of FIG. 10A and the area **171** of FIG. 10B are represented by A1 and A2, respectively. An area **1710** (namely, a difference between the areas represented by A1 and A2) is represented by A3.

Likewise, the number of photogenerated charges (namely, electrons generated due to an optical signal) per unit area and time have been represented by S1, S2 and S3 for the areas A1, A2 and A3, and are mathematically related as follows:

$$S3 = (A1*S1 - A2*S2)/A3$$

In this way, flexible (namely, programmable) charge-collection volumes of a pixel element can be used to increase the resolution of an image sensor, for example, by capturing multiple images with different patterns of the modulating voltages Vm.

Next, FIG. 10E is a schematic illustration of how the resolution can be improved with the aid of a larger matrix of pixel elements, in accordance with an embodiment of the present disclosure. FIG. 10E shows the matrix having M and N equal to 8.

With reference to FIG. 10E, pixel elements that satisfy $\text{mod}(2*(i-1)+j+1,5)=0$ have $V_m=V_{int_H}$, while other pixel elements have $V_m=V_{hq}$. A first picture Pic1 is captured using this modulating voltage pattern.

For illustration purposes only, there will now be considered that six pictures are captured using following modulating voltage patterns:

- Pic1: $V_m=V_{int_H}$ if $\text{mod}(2*(i-1)+j+1,5)=0$, else $V_m=V_{hq}$

- Pic2: $V_m = V_{int_H}$ if $\text{mod}(2*(i-1)+j+1,5)=1$, else $V_m = V_{hq}$
- Pic3: $V_m = V_{int_H}$ if $\text{mod}(2*(i-1)+j+1,5)=2$, else $V_m = V_{hq}$
- Pic4: $V_m = V_{int_H}$ if $\text{mod}(2*(i-1)+j+1,5)=3$, else $V_m = V_{hq}$
- Pic5: $V_m = V_{int_H}$ if $\text{mod}(2*(i-1)+j+1,5)=4$, else $V_m = V_{hq}$
- 5 - Pic6: $V_m = V_{hq}$

As a result, the first picture Pic1 has a pattern of V_m as shown in FIG. 10E; the second picture Pic2 has the same pattern shifted right by one position; the third picture Pic3 has the same pattern shifted down by one position; the fourth picture Pic4 has the same pattern shifted up by one position; the fifth picture Pic5 has the same pattern shifted right by one position; the sixth picture Pic6 is taken with $V_m = V_{hq}$ for all the pixel elements. These six pictures have enough information to virtually split all the pixel elements in five parts each in a manner that is similar to that shown in conjunction with FIGs. 10C and 10D. This yields in five times more pixel values than there are charge-collection nodes in the matrix. In effect, imaging speed is traded for resolution, a worthy trade-off, especially in good lighting conditions.

It will be appreciated that the pattern of the modulating voltages used in FIG. 10E is merely an example. As a charge-collection volume from which a given primary charge-collection node collects photogenerated charge can be changed electrically, various modulating voltage patterns and schemes can be introduced to boost the resolution. As an example, instead of using $V_m = V_{int_H}$ for the selected pixel elements while capturing the pictures Pic1, Pic2, Pic3, Pic4 and Pic5, $V_m = V_{lq}$ can be used for said selected pixel elements. In such a case, the pixel elements can be virtually split into four parts.

FIGs. 11A-C are still other example illustrations of how the quantum efficiency of pixel elements can be modulated to change their charge-collection volumes, pursuant to embodiments of the present disclosure. FIGs. 11A-C show top views of a portion of a matrix of pixel elements, in accordance with another embodiment of the present disclosure. For illustration purposes only, there will now be considered the matrix of pixel elements with $i=[1,M]$ rows and $j=[1,N]$ columns, wherein M and N are positive integers 4 and 5, respectively. With reference to FIGs. 11A-C, the pixel elements comprise a secondary charge-collection node in addition to a primary charge-collection node, for example as shown in FIG. 5A.

It is to be noted that the voltage polarities used here are based on an assumption that the first conductivity-type semiconductor is an n-type semiconductor.

With reference to FIG. 11A, all the pixel elements have their secondary charge-collection nodes in the high quantum-efficiency state, and have their primary charge-collection nodes in the low quantum-efficiency state. In other words, all the pixel elements have $V_x=V_{hq}$ and $V_m=V_{lq}$. Secondary charge-collection nodes of the pixel elements **100(2,3)** and **100(2,4)** collect photogenerated charge from charge-collection volumes beneath areas (shown enclosed by thick lines) **181** and **182**.

With reference to FIG. 11B, the quantum efficiencies of the primary charge-collection nodes of all the pixel elements are increased and/or the quantum efficiencies of the secondary charge-collection nodes of all the pixel elements is decreased. In other words, V_m is increased, while V_x is decreased, as compared to their previous values in FIG. 11A. The primary charge-collection nodes of the pixel elements **100(3,2)** and **100(3,3)** collect photogenerated charge from charge-collection volumes beneath areas (shown enclosed by thick lines) **183** and **184**. It will be appreciated

that the areas **181** and **182** have shrunk in size, as compared to FIG. 11A.

With reference to FIG. 11C, the quantum efficiencies of the primary charge-collection nodes of all the pixel elements are further increased
 5 and/or the quantum efficiencies of the secondary charge-collection nodes of all the pixel elements is further decreased, as compared to FIG. 11B. It is to be noted here that voltages V_x can be read out after the photogenerated charge has been collected; thus, the secondary charge-collection nodes can contribute to the resolution of the image sensor
 10 similar to the primary charge-collection nodes.

FIGs. 12A-D are schematic illustrations of the circuitry **107** of the pixel element **100**, in accordance with various embodiments of the present disclosure. For purposes of illustration, the first conductivity-type semiconductor material is assumed to be an n-doped semiconductor
 15 material; the operation with respect to the p-doped first conductivity-type semiconductor material could be explained in a similar manner. Preferably the semiconductor substrate **101** is a high-resistivity or intrinsic semiconductor material.

With reference to FIG. 12A, the pixel element **100** comprises a single
 20 primary charge-collection node **104** without any secondary charge-collection node. V_m is the modulating voltage of the modulating node **105** and is used to modulate the quantum efficiency of the primary charge-collection node **104**, whose voltage is V_c .

FIG. 12A shows only an exemplary part of the circuitry **107**, wherein the
 25 circuitry **107** comprises a switch **110**. In an example embodiment, the switch **110** can be implemented as an NMOS transistor, which is used to pull V_c towards the reset voltage V_r available at a node **112**. The switch **110** has a gate **111**. The circuitry **107** also comprises a capacitor **109** that is used to store the photogenerated collected charge. The capacitor

109 could be a dedicated capacitor, a parasitic capacitor or a combination of different capacitive elements.

The potential difference between the primary charge-collection node **104** and the backside conductive layer **108** is denoted by a label **113**. This
 5 potential difference should be high enough (typically, in an order of 15 volts) if a high-resistivity substrate is to be essentially fully depleted.

A matrix of such pixel elements **100** can be used to capture a picture as follows:

- First, the voltage V_c of the primary charge-collection nodes of all
 10 the pixel elements are initialized by pulling V_c towards the reset voltage V_r through the switch **110**, by asserting the voltage at the transistor gate **111**. In this example, V_r could be 5 V.
- Next, the voltage at the transistor gate **111** is de-asserted, and thus, the primary charge-collection nodes are left floating.
 15 Photogenerated charge starts to lower the voltage V_c at the primary charge-collection nodes from the initial value, which was approximately V_r . The modulating voltage V_m can be used to alter the quantum efficiency of the corresponding primary charge-collection nodes.
- Finally, after a certain integration time, the capacitor **109** holds a
 20 signal $V_r - V_c$ that is available for readout. The signal range could be, for example, 2V, so that the primary charge-collection nodes **104** would be at least at a potential that is 3V higher than the peripheral nodes **102**.

It will be appreciated that this is a simplified procedure for taking a picture. In real life, various techniques, for example, such as Correlated
 25 Double Sampling (CDS) in which the reset voltage value is read before the signal, can be used. Also, different pixel elements may have different integration times.

It is to be noted here that the voltage at the primary charge-collection node **104** should stay above a certain value in order to prevent a current from flowing between the peripheral node **102** (or the modulating node **105**) and the primary charge-collection node **104**, and, if applicable,
 5 keep the semiconductor substrate **101** essentially fully depleted. If the primary charge-collection node **104** is at a sufficiently high voltage, the primary charge-collection node **104** essentially isolates the modulating node **105** from the peripheral node **102**. The voltage polarities in the explanation below assume the first conductivity-type semiconductor
 10 material to be of an n-type semiconductor.

FIG. 12A is an example illustration of one possible way to restrict the voltage range of the primary charge-collection node **104** when the first conductivity-type semiconductor material is an n-type semiconductor. One way to prevent the voltage V_c at the primary charge-collection node
 15 **104** from becoming too low is to use the switch **110** to connect and disconnect the reset voltage V_r to/from the primary charge-collection node **104**. During reset, the transistor gate **111** of the switch **110** is pulled to a high voltage, so that the switch **110** is fully conducting, namely is turned ON. Then, the gate voltage can be set approximately to
 20 $V_{targ} + V_{th}$, wherein V_{targ} is a targeted lower bound of the voltage of the primary charge-collection node **104**, and V_{th} is a threshold voltage of the switch **110** (namely, the reset transistor). In this way, when the voltage at the primary charge-collection node **104** reaches V_{targ} , the gate-source voltage of the switch **110** is at V_{th} . If the voltage at the
 25 primary charge-collection node **104** further decreases, a current through the switch **110** is increased, essentially preventing the voltage at the primary charge-collection node **104** from lowering. In practice, such limiting happens gradually. It will be appreciated that V_{th} has been used in the above example just for illustration purposes.

With reference to FIG. 12B, the pixel element **100** comprises a primary charge-collection node **104** and a secondary charge-collection node **180**. The secondary charge-collection node **180** has the voltage V_x , and is connected to the circuitry **107** (said connection not shown in FIG. 12B).

- 5 The voltage V_x can be used to control the quantum efficiency of the secondary charge-collection node **180**.

With reference to FIG. 12C, the pixel element **100** comprises a single secondary charge-collection node **180**, without any primary charge-collection node. The secondary charge-collection node **180** can be reset
 10 with a switch **110_x**, which can be implemented as a transistor whose gate is controlled by the voltage at a node **111_x**. The reset voltage V_{r_x} is provided at a node **112_x**. The circuitry **107** also comprises a capacitor **109_x** for storing the charge. The pixel element **100** of FIG. 12C works much like the pixel element **100** of FIG. 12A, except that there is no
 15 modulating node. Herein, the modulation of the quantum efficiency is possible with V_{r_x} . If V_{r_x} is at a high voltage during reset, the quantum efficiency is high; similarly, if V_{r_x} is at a low voltage during reset, the quantum efficiency is low.

Assume that the capacitor **109_x** is reset, and then the node **111_x** is
 20 de-asserted. If the voltage at the node **112_x** is modulated at this point, some of that modulation connects capacitively through the capacitor **109_x** to the secondary charge-collection node **180**, resulting in a modulation of the quantum efficiency of the secondary charge-collection node **180**. This allows for modulation of the quantum efficiency during
 25 integration. Larger is the capacitance of the capacitor **109_x** relative to the total capacitance of the secondary charge-collection node **180**, higher is the capacitive modulation effect described above. Similarly, as was described in the example of FIG. 12A for the primary charge-collection node **104**, the voltage range of the secondary charge-collection node
 30 **180** can be restricted with the aid of the switch **110_x**.

With reference to FIG. 12D, the pixel element **100** comprises a primary charge-collection node **104** and a secondary charge-collection node **180**. The circuitry **107** comprises a switch **122_x**, which can be implemented by way of a transistor that is controlled by a gate **121_x**. The switch **122_x** connects the secondary charge-collection node **180** to a node **120** when the voltage at a node **121_x** is asserted. Similarly, the circuitry **107** further comprises a switch **122**, which can be implemented by way of a transistor that is controlled by a gate **121**. The switch **122** can connect the primary charge-collection node **104** to the node **120**. This means that pictures can be taken both with the secondary charge-collection node **180** and the primary charge-collection node **104**, and both store the charge into the capacitor **109**.

It will be appreciated that the pixel elements **100** shown in FIGs. 12A-D are only exemplary illustrations of the circuitry **107**. The principle described herein can be extended to other types of pixel elements having different numbers of primary charge-collection nodes and/or secondary charge-collection nodes. Notably, there can be more than one storage capacitor in a given pixel element. For example, in FIG. 12D, there could be a bank of capacitors that could store, for example, captured signals, reset values (for CDS) and derived signals.

FIG. 13 is a schematic illustration of the circuitry **107** of the pixel element **100**, in accordance with an embodiment of the present disclosure. With reference to FIG. 13, the pixel element **100** comprises first and second primary charge-collection nodes **104a** and **104b**, for example, as shown in FIG. 2A.

The pixel element **100** comprises a backside conductive layer **108** fabricated to be a backside of the semiconductor substrate **101**. The backside conductive layer **108** is biased to the bias voltage V_{bs} . The circuitry **107** comprises first and second switches **110a** and **110b** (which can be implemented by way of transistors) associated with the first and

second primary charge-collection nodes **104a** and **104b**, respectively. Similarly, transistor gates **111a** and **111b** of the switches **110a** and **110b** can be used to control the conductances of the switches **110a** and **110b**, respectively. The circuitry **107** further comprises storage
 5 capacitors **109a** and **109b**. A label **113a** represents potential differences between the charge-collection node **104a** and the backside conductive layer **108**, while a label **113b** represents potential differences between the charge-collection node **104b** and the backside conductive layer **108**. V_{r_a} and V_{r_b} are first and second reset voltages at nodes **112a** and
 10 **112b**, respectively.

Other parts (for example, such as possible source followers) of the circuitry **107** that may be used have not been shown in FIG. 13, for the sake of clarity only.

FIGs. 14A-B are schematic illustrations of how the collection of charge
 15 can be modulated, in the pixel element **100** of FIG. 13. The semiconductor substrate **101** is optionally a thinned high-resistivity substrate. It is assumed that the first conductivity-type semiconductor is an n-type semiconductor material. It is also assumed that the switches **110a** and **110b** are n-type transistors. Furthermore, a large enough
 20 potential difference **113a** and **113b** is arranged between the primary charge-collection nodes and the backside conductive layer **108** to essentially fully deplete the semiconductor substrate **101**. The switches **110a** and **110b** are used to pull the primary charge-collection nodes **104a** and **104b** close to their reset voltages V_{r_a} and V_{r_b} before an
 25 image capture starts. The storage capacitors **109a** and **109b** need not be dedicated capacitors, but can be formed, for example, by parasitic capacitances of the charge-collection nodes **104a** and **104b** and/or other attached components, for example, such as the transistor gates. It is to be noted here that the capacitors **109a** and **109b** could have different
 30 values, one could have a low capacitance (namely, a high conversion

gain) and the other could have a high capacitance (namely, a high full-well capacity), for example.

With reference to FIG. 14, it is assumed that the reset voltages V_{r_a} and V_{r_b} are 5V. The pixel signal range (namely, the voltage range of V_{c_a} , V_{c_b}) could be from 5V to 3V; in this case, the charge-collection nodes **104a** and **104b** would always be at least at a 3V higher potential than the peripheral node **102** (which is at the ground level). The bias voltage V_{bs} is -15V, V_{hq} is 2.5V and V_{lq} is 0V. The modulating voltage of 0V yields the low quantum-efficiency state, while the modulating voltage of 2.5V yields the high quantum-efficiency state to its corresponding primary charge-collection node.

With reference to FIGs. 14A-B, the primary charge-collection nodes **104a** and **104b** have been pulled towards the first and second reset voltages V_{r_a} and V_{r_b} using the switches **110a** and **110b** (by controlling the corresponding gate voltages **111a** and **111b**), respectively. After the reset operation, the switches **110a** and **110b** have been arranged to cut-off the operating region with the gate voltages **111a** and **111b** to prevent a further current flow between the drain nodes **112a** and **112b** and the primary charge-collection nodes **104a** and **104b**, respectively. The modulating voltages V_{m_a} and V_{m_b} can be at 2.5V ($=V_{hq}$) during the reset. The primary charge-collection nodes **104a** and **104b** compete for the photogenerated charge within the substrate **101**; charges that are collected by the primary charge-collection nodes **104a** and **104b** are stored to the capacitors **109a** and **109b**, respectively.

Next, the quantum efficiency modulation principle will be explained. FIG. 14A shows the pixel elements **100(2,2)** and **100(2,3)** within a matrix of $M=3$ rows and $N=4$ columns. The modulating voltage $V_{m_a}=V_{lq}$ and the modulating voltage $V_{m_b}=V_{hq}$. Approximate electric field lines **145** are shown in FIGs. 14A and 14B. The primary charge-collection node **104a** of the pixel element **100(2,2)** that is in the low quantum-efficiency

- state collects the photogenerated charge from a small volume circumscribed by a thick dashed line **125**, while the primary charge-collection node **104b** of the pixel element **100(2,2)** that is in the high quantum-efficiency state collects the photogenerated charge from a large volume of the substrate **101** between thick dashed lines **124** and **126** (excluding the volume circumscribed by the thick dashed line **125**). The charge that is photogenerated on the left side of the thick dashed line **124** is collected by the primary charge-collection node **104b** of the pixel element **100(2,1)**.
- Similarly, the primary charge-collection node **104a** of the pixel element **100(2,3)** collects photogenerated charge from a small volume circumscribed by a thick dashed line **127**, while the primary charge-collection node **104b** of the pixel element **100(2,3)** collects photogenerated charge from a large volume of the substrate **101** between a thick dashed line **126** and a line **124** (not shown) of the pixel element **100(2,4)** (excluding the volume circumscribed by the thick dashed line **127**). Thus, a fraction of charge that is photogenerated in the substrate **101** within a given pixel element may be collected by a neighbouring pixel element.
- In the pixel element **100** of FIG. 13, the primary charge-collection nodes **104a** and **104b** are close to each other (namely, the region **106** between said primary charge-collection nodes **104a** and **104b** is relatively thin), in order to minimize said charge collection by neighbouring pixel elements. It is to be noted here that the fill factor is essentially 100% because essentially all the charge generated beneath the pixel element is collected by one of the primary charge-collection nodes. It will be appreciated that if the substrate **101** of the pixel element **100** is essentially fully depleted as is assumed in FIGs. 14A and 14B, the photogenerated charge rapidly drifts to the primary charge-collection nodes **104a** and **104b**.

With reference to FIG. 14B, the pixel elements have $V_{m_a}=V_{hq}$ and $V_{m_b}=V_{lq}$. Charge-collection volumes from which the primary charge-collection node **104b** of the pixel element **100(2,2)** and the primary charge-collection node **104b** of the pixel element **100(2,3)** collect photogenerated charge are circumscribed by thick dashed lines **128** and **130**, respectively. Similar to FIG. 14A, the primary charge-collection node **104a** of the pixel element **100(2,3)** collects photogenerated charge from a large volume of the substrate **101** between thick dashed lines **129** and **131**, excluding the volume circumscribed by the thick dashed lines **130**.

It is interesting to note that if the incoming light goes through an infrared (IR) cut filter before reaching a relative thick (namely, in an order of tens of micrometres) thinned chip, the modulation contrast approaches 100%. This is because practically all short wavelength light gets absorbed near the backside and very little light gets absorbed in the vicinity of the primary charge-collection nodes that are in the low quantum-efficiency state (namely, volumes circumscribed by the thick dashed lines **125**, **127**, **128** and **130**), as the primary charge-collection nodes are located on the front side of the pixel elements.

FIG. 15 is a schematic illustration of how a small primary charge-collection node size can be obtained, whilst having a high modulation contrast and charge collection from the whole area of the pixel element **100**, in accordance with an embodiment of the present disclosure. FIG. 15 shows a schematic representation of a possible pixel readout circuitry that can be employed. A higher potential difference between the primary charge-collection nodes (**104a** and **104b**) and the peripheral node **102** allows for a smaller primary charge-collection node area in relation to the whole area of the pixel element **100**.

In an example case, the drain and source voltages at the nodes **112a**, **112b**, **114a**, **114b**, **119a** and **119b** of switches **110a**, **110b**, **115a**,

115b, **117a** and **117b**, respectively, are set, so that the reverse bias between the primary charge-collection nodes (**104a** and **104b**) and the peripheral node **102** is maximized, while keeping the transistor terminal voltages at a safe voltage range (namely, a voltage range that does not
5 harm the transistors).

It is to be noted here that the switches can be implemented by way of first conductivity-type transistors, for example, such as NMOS transistors that can be built into the peripheral node (p-well) **102**, so that the substrates of shutter transistors **122a** and **122b**, reset transistors **109a**
10 and **109b**, source follower transistors **115a** and **115b** and load transistors **117a** and **117b** are tied to the peripheral node **102**. The shutter transistors **122a**, **122b** are optional and are used to separate the primary charge-collection nodes **104a** and **104b** from storage nodes **120a** and **120b**, respectively. This provides one way of attaining global
15 shutter imaging.

Source followers formed by the transistors **115a** and **115b** and the transistors **117a** and **117b** buffer the signals stored on the capacitors **109a** and **109b**, respectively. These source followers have output nodes **116a** and **116b**. The shutter transistors **122a** and **122b** have gate nodes
20 **121a** and **121b**, having corresponding gate control voltages V_{sh_a} and V_{sh_b} , respectively. The gate control voltages V_{sh_a} and V_{sh_b} are used to turn the shutter transistors **122a** and **122b** to conducting or cut-off operation regions, respectively. The load transistors **117a** and **117b** have gate nodes **118a** and **118b**, which are used to set bias currents of
25 the source followers. The transistors **115a** and **115b** have drain terminals **114a** and **114b**, respectively. The transistors **117a** and **117b** have source terminals **119a** and **119b**.

During readout, the modulating voltages V_{m_a} and V_{m_b} are preferably set to predetermined values, in order to minimize fluctuations due to
30 capacitive connections between the modulating node **105a** and the

primary charge-collection node **104a**, as well as between the modulating node **105b** and the primary charge-collection node **104b**. After readout, the pixel element can be reset with the switches **110a** and **110b** that short circuit the nodes of the capacitors **109a** and **109b**. At this point
 5 the reset voltage at the nodes **120a** and **120b** can be read out or used within the pixel element to be used for double sampling or correlated double sampling.

It will be appreciated that FIG. 15 does not depict a complete pixel circuitry, and the use of the pixel element in an image sensor is not
 10 limited to the specific readout configuration explained above. In practice, implementing such pixel elements into an image sensor would also need separate selection devices connected to the gates **116a** and **116b**, in order to choose which pixel element out of a matrix of pixel elements is read out. Also, for example, the load transistors **117a** and **117b** could
 15 be placed in a peripheral circuitry (namely, a controller of the image sensor). Pixel element voltages such as those at the nodes **104a**, **104b**, **120a** and **120b** can be used for pixel-level signal processing and/or readout.

It is possible to increase the reset voltages V_{r_a} and V_{r_b} at the nodes
 20 **112a** and **112b** to, for example, 8V. This increases the potential difference between the primary charge-collection nodes (**104a** and **104b**) and the peripheral node **102** (including the region **106**). However, measures need to be taken to ensure that the transistors of the pixel circuit can handle such high voltages, as the transistors may nominally
 25 be, for example, designed to operate with 1.8V or 2.5V supplies. In one embodiment, applicable high and low supply voltages at the nodes **114a**, **114b**, **119a** and **119b** of the pixel circuitry of FIG. 15 can be set independently of the reset voltages at the nodes **112a** and **112b** and the peripheral node voltage at the peripheral node **102**. For example, if the
 30 reset voltages V_{r_a} and V_{r_b} are 8V, the voltage at the nodes **114a** and

114b could be 7.5V and the voltage at the nodes **119a** and **119b** could be 5V assuming the use of 2.5V transistors. In this way, the transistor terminal voltages would be in the allowed range. The non-zero body bias of the transistors would alter the threshold voltages, which would have
5 to be taken into account in terms of designing of the circuitry **107**.

As FIG. 15 shows an illustrative example of the principle behind designing the pixel circuitry, a real implementation could have different transistor circuits with a different number of independent supply voltages. It will be appreciated that the pixel circuitry is not restricted to this particular
10 configuration. If the conductivity types of the semiconductor materials are interchanged, the polarities of the voltage supplies also need to be interchanged. As an example, in case the first semiconductor material is a p-type semiconductor, and the second semiconductor material is an n-type semiconductor, the circuit **107** collects holes. Also, in such a case,
15 an n-type modulating node would be surrounded by a p-type primary charge-collection node. Furthermore, the voltage polarities would need to be changed if the semiconductor materials were interchanged, and the readout electronics (for example, such as transistors and the like) would need to be redesigned to take into account the changed voltage polarities
20 and voltage ranges. Moreover, if the first conductivity-type semiconductor material is a p-type semiconductor, the voltages at the charge-collection nodes **104a** and **104b** should stay below a certain value, in order to prevent a current from flowing between the peripheral node **102** and the charge-collection nodes **104a** and **104b**, respectively.

25 Next, FIG. 16 is a schematic illustration of an exemplary PTOF implementation of a system for capturing images, according to an embodiment of the present disclosure. In FIG. 16, there is shown an emitted signal, which is a light pulse **300** emitted by a light emitter of the system at a first moment of time. The emitted light pulse **300** hits a
30 target, and is reflected back from the target at a second moment of time.

The reflected light pulse is received as a received signal, which is detected as a light pulse **301** at the system. A time difference **302** between the edges of the emitted light pulse **300** and the received light pulse **301** represents the time of flight.

5 Measurements of the received signal are observed in separate measurement cycles. FIG. 16 shows three measurement cycles **305**, **306** and **307** (namely, x_1 , x_2 , x_3). The first measurement cycle **305** starts at the same time at which the light pulse **300** is emitted. The measurement cycle **305** is followed by the measurement cycles **306** and
 10 **307**. The received signal, due to the reflected light pulse **301**, is observed during reflected signal duration **303** and **304** in the measurement cycles **305** and **306**, respectively. It is to be noted here that the measurement cycle **307** is so much later in time that any measured signal is beyond a targeted distance range of the image sensor. Therefore, the
 15 measurement cycle **307** is likely to have only small amounts of the signal that is due to the emitted/reflected signal; it is dominated by background illumination, which represents a normal intensity image of a given scene.

It is well known [see reference Sensors 2015, 15, 4624-4642; doi:10.3390/s150304624] that a normalized distance can be obtained
 20 by a fraction $x_2 - x_3 / ((x_1 - x_3) + (x_2 - x_3))$. It is to be noted here that the denominator represents the total received reflected signal.

Optionally, the aforementioned three measurements could be carried out by having a sensor circuit with three modulated charge-collection nodes, which could be laid out next to each other, for example, as shown in FIG.
 25 4A. In such a case, after repeated measurements with multiple emitted pulses and repeating cycles **305**, **306** and **307**, the charge-collection nodes aggregate a sufficient amount of charge. The charge-collection nodes **104a** and **104b** of FIG. 4A yield the values of x_1 and x_2 , while and the charge-collection node **104c** of FIG. 4A yields the value of x_3
 30 (background) in a similar fashion.

Such a multi-mode image sensor that is capable of detecting multiple modalities (for example, such as the ToF and intensity image) is highly useful in enabling novel image capture/processing schemes. It is to be noted here that the signal captured during x_3 at the charge-collection node **104c** is a conventional intensity image without a contribution of the emitted signal. In one embodiment, pixel-parallel signal processing is applied to compute the ToF result as follows: $x_2 - x_3 / ((x_1 - x_3) + (x_2 - x_3))$, which is used in focal plane processing, together with a normal intensity image.

In one embodiment, while the image sensor acquires the signal, the pixel circuitry carries out computation on the signals of the pixel element (for example, the voltages of primary and/or secondary charge-collection nodes, the voltages of the storage elements, the voltages of the modulating nodes, and so on), thereby resulting in derived values. When a local pixel voltage (or current) signal, or derived values, or pixel signal/signals or derived values in a specific pixel element or a pixel neighbourhood meets certain criteria, the pixel circuitry can detect that such criteria are met, and may signal to the outside of the matrix that it has information ready for readout. Preferably, selected signal values of the pixel element, or pixel elements in the neighbourhood of the pixel element that meet certain criteria, are read out of the matrix of pixel elements, while other pixel elements may continue capturing the signal. Selected signals may also be stored at the time the pixel neighbourhood meet the certain criteria. It is to be noted here that the principle of monitoring pixel signals and/or neighbour pixels signals or a function of these signals, determining locally when a certain condition is met and requesting/serving readout of the pixel signal and/or the neighbour pixels signals, and/or storing selected signals locally based on the certain criteria is a general way of computing and applies beyond the modulated image sensor of embodiments of the present disclosure.

FIG. 17 is a flowchart depicting the principle described above. In the flowchart, phases **400**, **401**, **402** and **403** indicate different operational phases of the circuitry within a given pixel element.

In the phase **400** (namely, an image capture phase), the total received
 5 reflected signal that originates from the emitted signal is computed using two Operational Transconductance Amplifiers (OTA s) **404** and **405**, and the result is compared with a current-mode comparator **407** to a threshold value. Optionally, said threshold value is tunable; an apparatus for creating the threshold value is internal to the current-mode
 10 comparator **407** and is not shown in FIG. 17.

It is to be noted here that in the phase **400**, there is a voltage COMP controls switch transistor between **404**, **405** and **407**, so that the outputs of the OTA s **404** and **405** and the input of the current-mode comparator **407** are connected together. When the outputs of the OTA s
 15 **404** and **405** are connected together, the resulting sum current represents $((x1-x3)+(x2-x3))$, namely, the total reflected signal that originates from the light source (for example, a light emitter).

Once said sum current is above a threshold (that is selected to ensure distance measurement quality), there is enough signal to reliably
 20 determine the distance, and transition to the phase **401** takes place. In the phase **401**, a read request (RD_REQ) is signalled for. It is to be noted here that alternatively or additionally to the readout request, the phase **401** could also activate other functionalities, for example, such as a local storage process, not shown in FIG. 17.

25 In the phase **401**, the circuit waits for a read acknowledgement signal RDa from a peripheral circuit; once RDa is received, the circuit moves to a readout state, namely the phase **402**.

In the phase **402**, $x1-x3$ (RDa active) and $x2-x3$ (RDb active, driven by a peripheral circuitry) can be read out from a node PIX_OUT **409** (or stored locally) through switch transistors that are controlled by signals RDa and RDb. After the readout, the circuit moves to the phase **403**.

- 5 In the phase **403**, the circuit can be reset. In this regard, an autozero operation to a cancel OTA offsets can be performed, if desired. Afterwards, the circuit returns to the phase **400** to wait for a new condition in which there is enough signal for a reliable distance measurement. Alternatively, instead of the readout as shown in the phase
- 10 **402**, the fraction $x2-x3/((x1-x3)+(x2-x3))$ can be computed at a pixel level so that the distance information is readily available, for example, for pixel-level processing.

FIG. 18 is a schematic illustration of an exemplary Global-Shutter (GS) imaging implementation of a system for capturing images, according to

15 an embodiment of the present disclosure. In the GS imaging, incoming light is collected also during readout. In other words, essentially no incoming signal is lost during readout. The GS imaging can be performed so that readout and image capture can be carried out simultaneously.

It is to be noted here that shutter transistors (for example, **121a** and

20 **121b** shown in FIG. 15) are not needed in the GS imaging, provided that the modulation contrast is high enough. Therefore, for illustration purposes herein, it is assumed that the shutter transistors can be omitted. The principle being the GS imaging implementation can be understood with the aid of FIGs. 18 and 13.

25 FIG. 18 shows the operation during different phases of voltage pulses Vm_a and Vm_b applied to the modulating nodes **105a** and **105b** of the pixel element **100** of FIG. 13, respectively. During a modulation pulse phase **502** (Vm_a HI), the primary charge-collection node **104a** collects the charge of a frame 1 to the capacitor **109a**. At the same time, at a

modulation pulse phase **500** (V_{m_b} LO), the primary charge-collection node **104b** first waits for readout, then a frame 0 is read out from the primary charge-collection node **104b**, the capacitor **109b** is reset, and the reset value of the capacitor **109b** is read out. Thereafter, during a
 5 modulation pulse phase **503** (V_{m_b} HI), a frame 2 is captured, while at the same time, during a modulation pulse phase **501** (V_{m_a} LO), the circuit waits for readout, then the frame 1 is read out from the capacitor **109a**, the capacitor **109a** is reset, and the reset value of the capacitor **109a** is read out. These phases are repeated continuously. It is to be
 10 noted here that the reset values are read out to be used for (correlated) double sampling that uses the reset and signal values.

If shutter transistors were used, they would be in a conducting mode during the modulation pulse phases **502** and **503**, and they would be turned to a cut-off region (namely, a sample signal to the capacitors
 15 **109a** and **109b**) in the beginning of the modulation pulse phases **500** and **501**. Sampling a capacitor fixes the capacitor thermal noise to on average kT/C . If no shutter transistors are used, such sampling does not take place at the pixel level. Since there are various ways to reduce the thermal noise in the readout path (namely, read noise) at a column level,
 20 embodiments of the present disclosure have potential to very low noise global-shutter imaging that does not waste essentially any incoming light.

In an embodiment, the image sensor is used for High-Dynamic Range (HDR) imaging. The modulating voltages V_{m_a} and V_{m_b} connected to the modulating nodes **105a** and **105b** (shown, for example, in FIG. 13)
 25 can be modulated repeatedly during one frame so that the duty cycles of the two modulation sources are different. As an example, the primary charge-collection node **104a** can be kept much longer in the high quantum-efficiency state as compared to the primary charge-collection node **104b**. This means that the primary charge-collection node **104a**
 30 can capture more signal than primary charge-collection node **104b**. Both

signals, corresponding to the same image frame, can then be read out of the image sensor.

The same circuit that can be used for the HDR imaging works also with the GS imaging without any need for modifications. It is also possible to
5 combine GS imaging and HDR imaging as GSHDR imaging by using different integration times for the two primary charge-collection nodes **104a** and **104b** in the GS imaging implementation described above. As an example, the modulation pulse phases **502** and **503** of FIG. 18 could be of different lengths. In this way, every other frame would be captured
10 with a different integration time, and these GS images could be combined to generate an HDR image.

It will be appreciated that the GS imaging and the GSHDR imaging schemes explained above do not need a fast modulation of the quantum efficiency; the modulation needs not be altered during the same
15 integration cycle. Therefore, a secondary charge-collection node could also be used in place of the primary charge-collection nodes **104a** and/or **104b**. The quantum efficiencies of the secondary charge-collection nodes could be modulated by reset voltages V_{r_x} , for example.

In one embodiment, the image sensor pursuant to embodiments of the
20 present disclosure can be applied for Signal-to-Background Ratio (SBR) improvement. In this embodiment, the aforementioned system comprises a light emitter with a pulsed light field that has a low duty cycle. In this context, the term *background* generally refers to any captured signal component that does not originate from a signal emitted
25 by the light emitter. As compared to light sources that are ON all the time, the light emitter employs a pulsed, low duty cycle that helps to improve the SBR, while coping with average emitted power and emitted pulse power regulations. FIG. 19 is a schematic illustration of an exemplary implementation of the aforementioned light emitter with a
30 pulsed light field in the aforementioned system, according to an

embodiment of the present disclosure. The SBR is improved versus an average emitted power; such improvement is possible by pulsing the emitted light and collecting the photogenerated charge due to reflected emitted light to one group of primary charge-collection nodes, while incoming signal that is due to ambient/background illumination is collected to another group of primary charge-collection nodes. It is to be noted here that in a multi-mode image sensor, the signal due to ambient/background illumination can be used as a conventional intensity image.

In FIG. 19, an emitted signal **600** is a pulsed light field that has a low duty cycle. A received signal **601** is reflected back from a target in a given scene. It is assumed that the charge-collection nodes **104a** and **104b** are initially reset, and, if applicable, reset values are read out for CDS. The image sensor is modulated in such a way that the modulating voltage V_{m_a} goes high with the emitted signal **600**, and stays high for a duration t_1 , as indicated by a label **602**; the duration t_1 is the time taken for the signal to be reflected from the maximum distance of interest. After that, the modulating voltage V_{m_b} goes high (namely, the primary charge-collection node **104b** goes to the high quantum-efficiency state) for a duration t_2 , as indicated by a label **603**. This cycle of pulsing the light source and capturing the reflected energy due to the emitted pulse is repeated for N cycles, where N is large enough to guarantee enough signal to be accumulated on the capacitor **109a**. The timing needs to satisfy $t_1 < t_2$, and preferably $t_1 \ll t_2$. This is because the emitted light during a given pulse can be approximately t_2/t_1 times higher than that emitted by a continuous light source. After the N cycles, the voltage across the capacitor **109a** represents the signal due to the reflected light field. It is to be noted here that the voltage across the capacitor **109b** corresponds to a normal intensity image of the given scene (namely, without the reflected light field), which can also be read out and used, yielding a multi-mode image sensor.

It will be appreciated that various light field applications like range imaging (see Background of the present disclosure for examples) could benefit from the SBR improvement implementation described above.

In one embodiment, the aforementioned system is employed for spectral
5 imaging purposes. In this case, light fields of different wavelengths are emitted and spectral imaging is performed. Optionally, colour images are obtained without using colour filters, by emitting duty-cycled pulses of three primary colours and by collecting the reflected light due to light fields of the different colours to different primary charge-collection nodes.
10 Again, such duty cycling would help reduce received signals that originate from background illumination. As an example, three colour imaging would require four primary charge-collection nodes, one for each colour and one for collecting light between pulses for the duration t_2 . Such an arrangement would give a normal intensity image in addition to colour
15 information. Spectral imaging could be applied, for example, for biometry applications and active vision.

It is to be noted here that with the image sensor pursuant to embodiments of the present disclosure, it is also possible to identify the amount of pulse signal while the signal is being captured as was done for
20 ToF signals in FIG. 16. Monitoring the captured signal makes it possible to implement event-based readout (or local storage) for pixels where sufficient signal has been captured. Optionally, the pixel switches from capture to readout states in a self-triggering way. In other words, the state transitions are optionally hard-coded in the pixel circuits, resulting
25 in Multiple Instruction, Multiple Data (MIMD) operation. Furthermore, it is possible that each pixel be reset after its event-based readout (namely, frameless operations). It will be appreciated that similar approach can be applied to pixel-level processing in general.

FIG. 20A is a schematic illustration of multi-mode imaging capabilities of
30 the pixel circuit, in accordance with various embodiments of the present

disclosure. In Fig. 20A, there is shown a timing diagram **700** for a sensor operation that could be used to measure one phase in MTOF imaging, according to a first embodiment of the present disclosure. The timing diagram **700** shows how the use of shutter switches could be avoided,
5 how the image sensor could be used as a multi-mode image sensor that captures also normal intensity image in addition to the modulated ToF data, and how the average emitted light power could be maintained, while increasing instantaneous emitted light power as to increase signal-to-background level.

10 A pixel element, for example like that of FIG. 15, could be used in the first embodiment. The emitted signal is a repetitive sinusoidal signal; however, it can also take other shapes, for example, such as a rectangular pulse shape. In the timing diagram **700**, charge is collected to the primary charge-collection nodes **104a** and **104b**. Once a sufficient
15 amount of pulses has been emitted and the corresponding photogenerated charge has been accumulated into the capacitors **109a** and **109b**, shutter transistors **122a** and **122b** are turned to cut-off, and readout of voltages from the nodes **120a** and **120b** is carried out. A problem with using a shutter transistor is that once the switches **110a**
20 and **110b** turn off, kT/C noise is sampled into the capacitors **109a** and **109b**. Increasing the capacitance values of the capacitors **109a** and **109b** reduces kT/C noise, but lowers the sensitivity, namely the conversion gain (V/electron).

In FIG. 20A, there is shown another timing diagram **701** according to a
25 second embodiment of the present disclosure, wherein the pixel element comprises a third primary charge-collection node **104c** in addition to the primary charge-collection nodes **104a** and **104b**, for example as illustrated in FIG. 4A. In this case, shutter transistors are not needed at all; they can either be kept on all the time (assuming a high enough
30 modulation contrast), or be left out of the pixel circuit. The signal is

accumulated to the charge-collection nodes **104a** and **104b**. After the accumulation, the quantum efficiency of the third primary charge-collection node **104c** is modulated to a high level with the modulating voltage V_{m_c} applied to the modulating node **105c**, and the primary charge-collection nodes **104a** and **104b** are read out. It is to be noted here that capturing of an instantaneous value of the kT/C noise due to sampling with shutter transistors is eliminated allowing further continuous time noise bandwidth suppression in the signal path, thereby reducing a Root Mean Square (RMS) value of the noise associated with that particular capacitance. It is to be further noted that in the second embodiment described above, the third primary charge-collection node **104c** has been used to eliminate the need for shutter transistors; however, a secondary charge-collection node **180** can be used in place of the third primary charge-collection node **104c**, where the voltage V_x of the secondary charge-collection node **180** is used to control the quantum efficiency of the secondary charge-collection node **180**. An example embodiment of such an arrangement of charge-collection nodes is shown in FIG. 20B, wherein the pixel element **100** comprises two primary charge-collection nodes **104a** and **104b** and a secondary charge-collection node **180** arranged between the primary charge-collection nodes **104a** and **104b**. Also, the timing of V_x is shown in the timing diagram **701**.

In FIG. 20A, there is shown yet another timing diagram **702** according to a third embodiment of the present disclosure, wherein the pixel element comprises three primary charge-collection node **104a**, **104b** and **104c**, for example as illustrated in FIG. 4A, wherein the third primary charge-collection node **104c** has an associated shutter transistor **122c** (whose drain is denoted by **120c**) and a storage capacitor **109c**. It is to be noted here that the shutter transistor **122c** and the capacitor **109c** are not shown in FIG. 4A; however, they are arranged in a manner that

is similar to an arrangement of the shutter transistor **122a**, the drain **120a** and the capacitor **109a** shown in FIG. 15.

The timing diagram **702** is similar to the timing diagram **701**, except that after charge is first accumulated to the primary charge-collection nodes **104a** and **104b**, charge is then accumulated to the primary charge-collection node **104c** by modulating the quantum efficiency of the third primary charge-collection node **104c** to a high level with the modulating voltage V_{m_c} applied to the modulating node **105c**, followed by turning the shutter transistor **122c** to cut-off. Now, the primary charge-collection nodes **104a** and **104b** contain a phase signal to be used for the ToF measurement, whereas the voltage across the storage capacitor **109c** contains a normal intensity image (namely, a global shutter image). Signals from the primary charge-collection nodes **104a** and **104b** are readout when the primary charge-collection node **104c** is in the high quantum-efficiency state. After this, the shutter transistor **122c** is turned to a cut-off region and the voltage across the storage capacitor **109c** can be read out. Similar to the timing diagram **701**, the third primary charge-collection node **104c** could be replaced with a secondary charge-collection node **180** and a corresponding shutter transistor, for example as shown in FIG. 20B.

The exemplary implementation described above can be extended to various different configurations of pixel elements. As an example, there could be two primary charge-collection nodes that would collect the ToF information, a first secondary charge-collection node that would capture the conventional image (without shutter transistor) and a second secondary charge-collection node that would capture the signal when the first secondary charge-collection node is being read out.

In FIG. 20A, there is shown still another timing diagram **703** for a variant of ToF phase capture procedure, according to a fourth embodiment of the present disclosure, wherein an aim is to improve the SBR in modulated

ToF imaging. In the fourth embodiment, the emitted signal is turned off between separate sets of emitted pulses. When the emitted signal is inactive, charge is collected by the primary charge-collection node **104c** of the pixel element **100** of FIG. 4A. This way, the average emitted signal
5 can be kept low enough to meet eye safety regulations, while having a higher transmission power during pulses. It will be appreciated that other variants are also possible. For example, in one variant, the primary charge-collection node **104c** is accompanied with the shutter transistor **122c** and the capacitor **109c**. By turning off the shutter transistor **122c**
10 after the accumulation into the capacitor **109c**, it is possible to read out the voltage at the drain **120c** as the intensity image.

It will be appreciated that various exemplary implementations proposed in the present disclosure, for example, including the ToF imaging, the light field imaging and the resolution enhancement do not necessarily
15 need the modulated image sensor pursuant to embodiments of the present disclosure. Notably, the image sensor can be implemented in various different ways to steer collected charge to different charge-collection nodes.

While embodiments of the present disclosure have been described with a
20 number of exemplary implementations, it will be appreciated that various modifications, and equivalent arrangements, which fall within the scope of the prospective claims are possible.

Modifications to embodiments of the present disclosure described in the foregoing are possible without departing from the scope of the present
25 disclosure as defined by the accompanying claims. Expressions such as including , comprising , incorporating , have , is used to describe and claim the present disclosure are intended to be construed in a non-exclusive manner, namely allowing for items, components or elements not explicitly described also to be present. Reference to the singular is
30 also to be construed to relate to the plural.

CLAIMS

What is claimed is:

1. A pixel element (100) comprising:
 - a semiconductor substrate (101) of a first or second conductivity type, the semiconductor substrate (101) having a front side and a backside, wherein the semiconductor substrate (101) is configured to be exposed to a flux of photons, and to convert the flux of photons to first and second conductivity-type mobile charges;
 - a first primary charge-collection node (104, 104a) of a first conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate (101);
 - at least one peripheral node (102) of a second conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate (101), wherein the at least one peripheral node (102) at least partially surrounds the first primary charge-collection node (104, 104a);
 - a circuitry (107) directly connected to the first primary charge-collection node (104, 104a) and to the at least one peripheral node (102), wherein the circuitry (107) comprises:
 - a first switch (110a, 122a) to connect and disconnect a first reset voltage (V_r , V_{r_a}) to/from the first primary charge-collection node (104, 104a);
 - means to provide a peripheral node voltage to the at least one peripheral node (102); and
 - a first measurement means to measure an amount of the first conductivity-type mobile charges collected by the first primary charge-collection node (104, 104a);
 - a backside conductive layer (108) arranged on the backside of the semiconductor substrate (101), configured to collect and conduct the second conductivity-type mobile charges, and configured to be electrically connected to a bias voltage (V_{bs}); and

- a first modulating node (105, 105a) of the second conductivity-type semiconductor material, wherein the first modulating node (105, 105a) is:

- 5 - arranged on the front side of the semiconductor substrate (101);
- at least partially surrounded by the first primary charge-collection node (104, 104a), which first primary charge-collection node is arranged to provide electrical isolation between the first modulating node (105, 105a) and the at least one peripheral node (102); and
- 10 - electrically connected to a first modulating voltage (V_m , V_{m_a}) source, which first modulating voltage source is independent of the peripheral node voltage.

2. A pixel element (100) according to claim 1, further comprising a
15 second primary charge-collection node (104b) or a secondary charge-collection node (180) of the first conductivity-type semiconductor material, arranged on the front side of the semiconductor substrate (101).

3. A pixel element (100) according to claim 2, further comprising a
20 second modulating node (105b) of the second conductivity-type semiconductor material, wherein the second modulating node (105b) is:

- arranged on the front side of the semiconductor substrate (101);
- 25 - at least partially surrounded by the second primary charge-collection node (104b), which second primary charge-collection node is arranged to provide electrical isolation between the second modulating node (105b) and the at least one peripheral node (102); and

- electrically connected to a second modulating voltage (V_{m_b}) source, which second modulating voltage source is independent of the peripheral node voltage; and

wherein the circuitry (107) further comprises:

- 5 - a second switch (122b, 110b) to connect and disconnect a second reset voltage (V_{r_b}) to/from the second primary charge-collection node (104b); and
- a second measurement means to measure an amount of the first conductivity-type mobile charges collected by the second
- 10 primary charge-collection node (104b).

4. A pixel element (100) according to any of the preceding claims, wherein the semiconductor substrate (101) is a high resistivity substrate having a doping concentration of at most $1e14$ atoms/cm³.

5. A pixel element (100) according to claim 4, wherein the
15 semiconductor substrate (101) is a high resistivity substrate having a doping concentration of at most $5e13$ atoms/cm³.

6. A pixel element (100) according to any of the preceding claims, wherein the pixel element (100) is arranged to receive a flux of photons from the backside of the semiconductor substrate (101).

20 7. A method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element (100), the pixel element (100) comprising a semiconductor substrate (101), a first primary charge-collection node (104a), a second primary charge-collection node (104b), a first modulating node (105a), a second
25 modulating node (105b) and a circuitry (107) comprising a first switch (110a) and a second switch (110b), the method comprising:

- (i) depleting a volume inside of the semiconductor substrate (101) by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate (101) by at least 50 %;
- (ii) providing a first reset voltage (V_{r_a});
- 5 (iii) providing a second reset voltage (V_{r_b});
- (iv) resetting the first primary charge-collection node (104a) by:
 - connecting the first primary charge-collection node (104a) to the first reset voltage (V_{r_a}) by turning the first switch (110a) ON; and
 - 10 - disconnecting the first primary charge-collection node (104a) from the first reset voltage (V_{r_a}) by turning the first switch (110a) OFF;
- (v) resetting a second primary charge-collection node (104b) by:
 - connecting the second primary charge-collection node (104b) to the second reset voltage (V_{r_b}) by turning a second switch (110b) ON; and
 - 15 - disconnecting the second primary charge-collection node (104b) from the second reset voltage (V_{r_b}) by turning the second switch (110b) OFF;
- 20 (vi) accumulating the first conductivity-type mobile charges to the first and second primary charge-collection nodes during a cycle of:
 - decreasing a first charge-collection volume by setting a first modulating voltage (V_{m_a}) to a value that increases a first reverse bias voltage between the first primary charge-collection node (104a) and the first modulating node (105a), and increasing a
 - 25 second charge-collection volume by setting a second modulating voltage (V_{m_b}) to a value that decreases a second reverse bias voltage between the second primary charge-collection node (104b) and the second modulating node (105b);
 - 30 - waiting for a first period of time;

- after the first period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_{m_a}) to a value that decreases the first reverse bias voltage between the first primary charge-collection node (104a) and the first modulating node (105a), and decreasing the second charge-collection volume by setting the second modulating voltage (V_{m_b}) to a value that increases the second reverse bias voltage between the second primary charge-collection node (104b) and the second modulating node (105b); and
 - waiting for a second period of time; and
- (vii) measuring the amount of the first conductivity-type mobile charges accumulated during the cycle of the step (vi) by determining voltage levels (V_{c_a} , V_{c_b}) of the first primary charge-collection node (104a) and the second primary charge-collection node (104b).
8. A method according to claim 7, wherein the pixel element (100) further comprises a peripheral node (102), the method further comprising arranging for the peripheral node (102) to have a potential sufficient for providing at least a 0.6 volt potential barrier to the first conductivity-type charge carriers between the first and the second primary charge-collection nodes when the first and second primary charge-collection nodes are at the first and second reset voltages.
9. A method for measuring an amount of first conductivity-type mobile charges associated with a flux of photons received by a pixel element (100), the pixel element (100) comprising a semiconductor substrate (101), a first primary charge-collection node (104), a secondary charge-collection node (180), a first modulating node (105), a peripheral node (102) and a circuitry (107) comprising a first switch (110), the method comprising:

- (a) depleting a volume inside of the semiconductor substrate (101) by setting a bias voltage (V_{bs}) to a value that depletes the volume of the semiconductor substrate (101) by at least 50 %;
- (b) providing a first reset voltage (V_r);
- 5 (c) providing a third voltage (V_x);
- (d) resetting the first primary charge-collection node (104) by:
 - connecting the first primary charge-collection node (104) to the first reset voltage (V_r) by turning the first switch (110) ON; and
 - 10 - disconnecting the first primary charge-collection node (104) from the first reset voltage (V_r) by turning the first switch (110) OFF;
- (e) accumulating the first conductivity-type mobile charges to the first primary charge collection node (104) and the secondary charge-collection
 - 15 node (180) during a cycle of:
 - decreasing a first charge-collection volume by setting a first modulating voltage (V_m) to a value that increases a first reverse bias voltage between the first primary charge-collection node (104) and the first modulating node (105), and increasing a second
 - 20 charge-collection volume by setting the third voltage (V_x) to a value that increases a third reverse bias voltage between the secondary charge-collection node (180) and the peripheral node (102);
 - waiting for a third period of time;
 - 25 - after the third period of time, increasing the first charge-collection volume by setting the first modulating voltage (V_m , V_m) to a value that decreases the first reverse bias voltage between the first primary charge-collection node (104) and the first modulating node (105), and decreasing the second charge-
 - 30 collection volume by setting the third voltage (V_x) to a value that

decreases the third reverse bias voltage between the secondary charge-collection node (180) and the peripheral node (102); and

- waiting for a fourth period of time; and

(f) measuring the amount of the first conductivity-type mobile charges
5 accumulated during the cycle of the step (e) by determining a voltage level (V_c) of the first primary charge-collection node (104).

10. A method according to claim 9, further comprising arranging for the peripheral node (102) to have a potential sufficient for providing at least a 0.6 volt potential barrier to the first conductivity-type charge carriers
10 between the first primary charge-collection node (104) and the secondary charge-collection node (180) when the first primary charge-collection node (104) and the secondary charge-collection node (180) are at the first reset voltage (V_r) and the third voltage (V_x).

11. A system for capturing images, the system comprising an image
15 sensor, wherein the image sensor comprises a matrix of pixel elements (100) according to any of claims 1 to 6 and a controller, the pixel elements (100) being connected to the controller.

12. A system according to claim 11, further comprising a light emitter
20 arranged to be directed to a target, wherein the controller is configured to:

- provide a control signal for the light emitter to emit a pulse of photons at a first moment of time;

- start a measurement to detect a reflected pulse of photons from the target with a first pixel element of the matrix of pixel elements at a
25 second moment of time;

- stop the measurement with the first pixel element at a third moment of time;

- start a measurement to detect the reflected pulse of photons from the target with a second pixel element of the matrix of pixel elements at a fourth moment of time;
- stop the measurement with the second pixel element at a fifth
5 moment of time; and
- calculate a time of flight of the pulse of photons, by comparing an amount of accumulated first conductivity-type mobile charges associated with the reflected pulse of photons in the first pixel element with an amount of accumulated first conductivity-type mobile charges associated
10 with the reflected pulse of photons in the second pixel element.

13. A system according to claim 11 or 12, further comprising a light emitter configured to emit light pulses at more than one wavelength, wherein the controller is further configured to adjust modulating voltages (V_m) of modulating nodes of individual pixel elements of the matrix of
15 pixel elements based upon a given wavelength emitted by the light emitter at a given moment of time.

14. A system according to any of claims 11 to 13, wherein the controller is configured to control the modulating voltages (V_m) based upon pulse duration of the emitted light pulses to:

- 20 - arrange a first charge-collection volume of a first size for a first pulse duration; and
 - arrange a second charge-collection volume of a second size for a second pulse duration,
- wherein the first size is larger than the second size, and the first pulse
25 duration is smaller than the second pulse duration.

15. A system according to claim 11, wherein the system is a camera.

16. A system according to any of claims 11 to 14, wherein the system is a lidar.